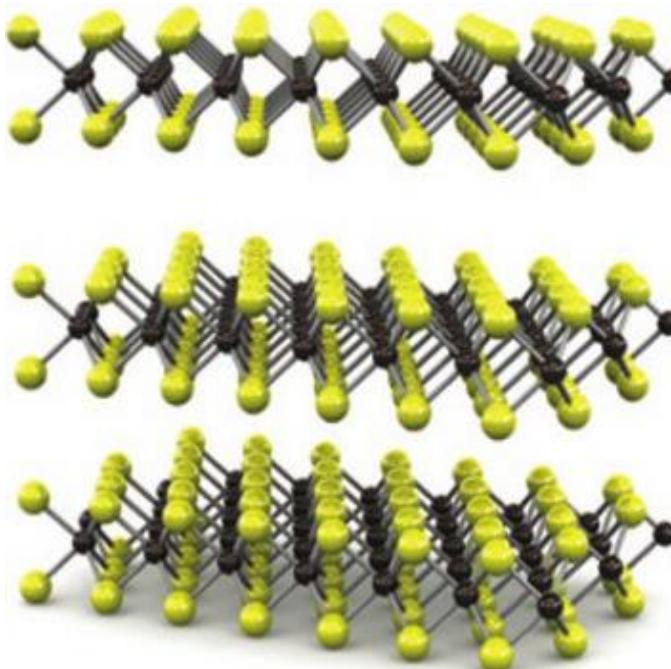


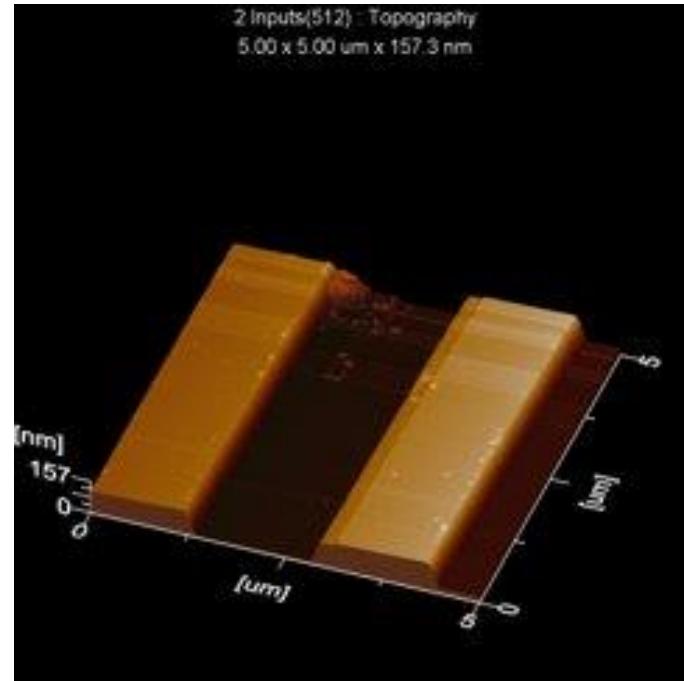
# With Molybdenum Disulfide into the World of 2D-Materials

Björn Schäfer

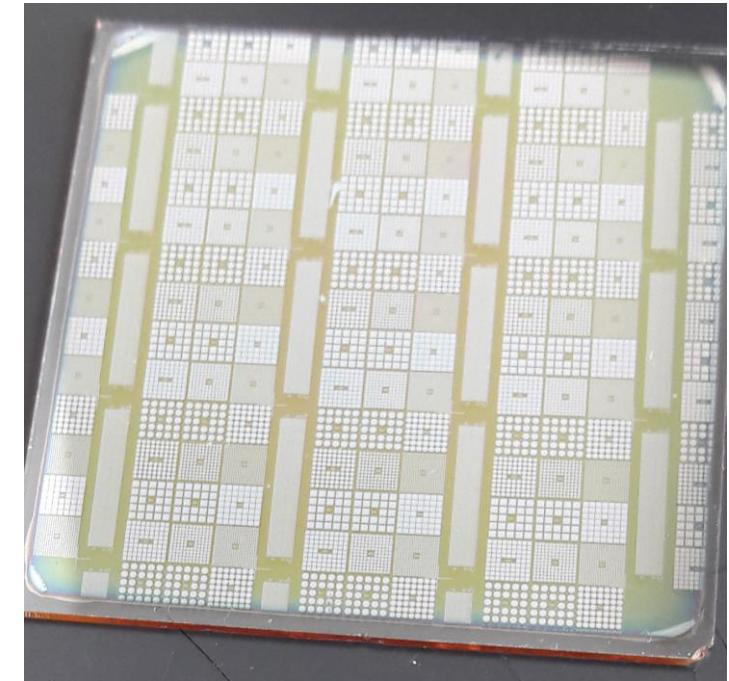
MoS<sub>2</sub>



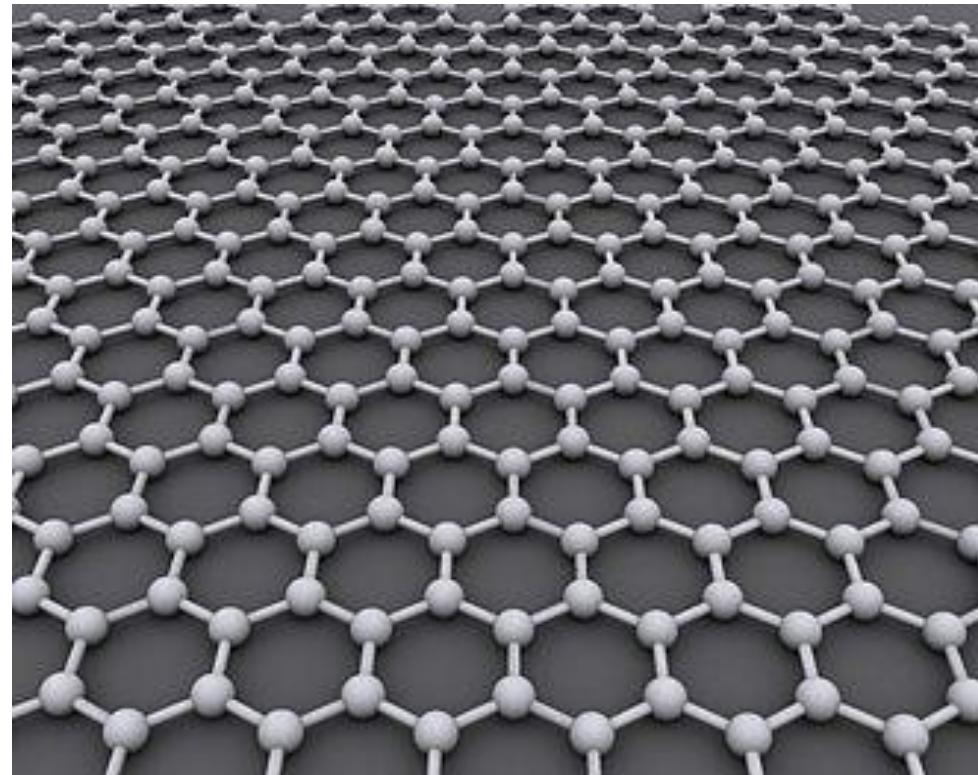
Thickness determination



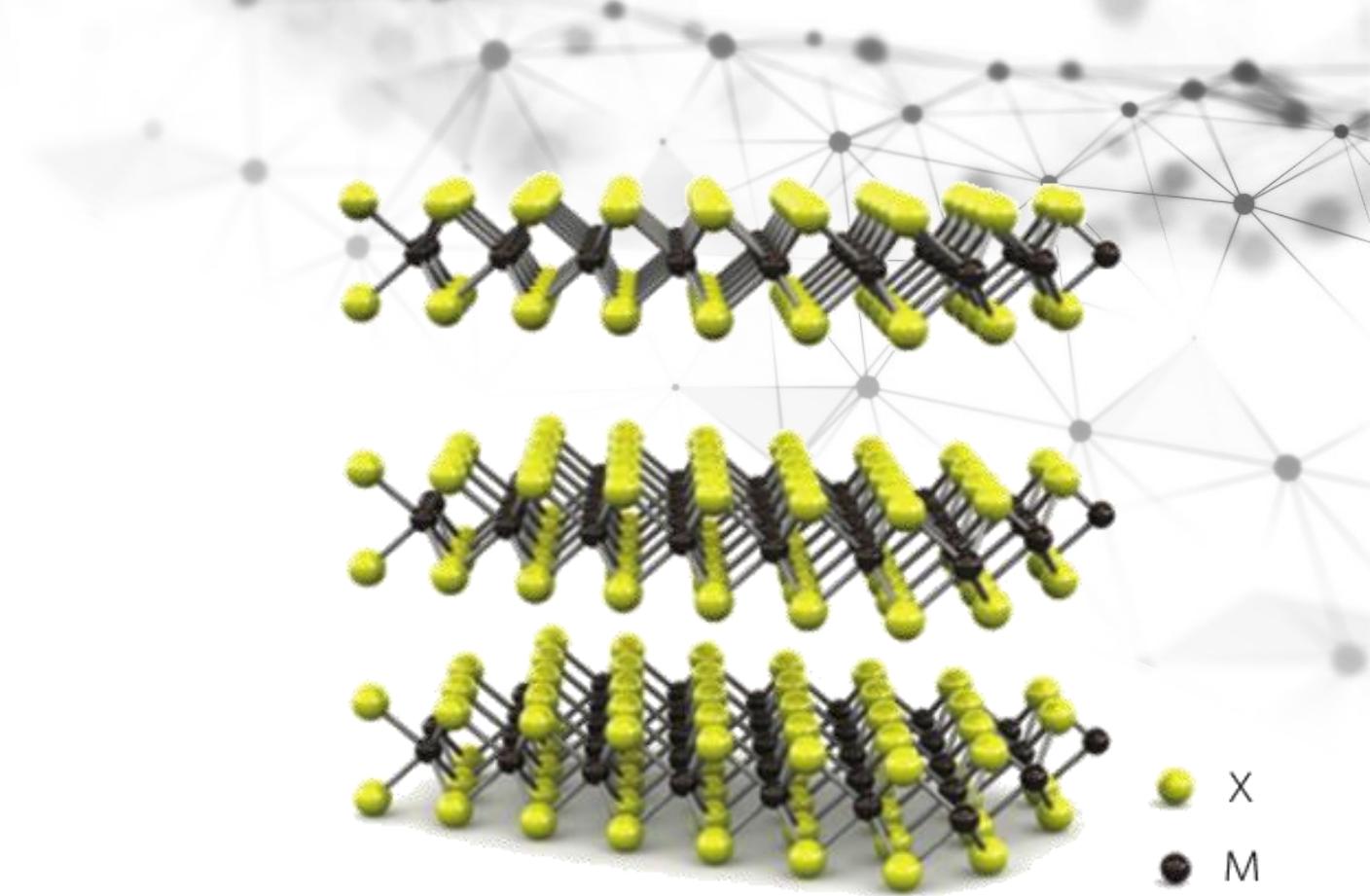
Device integration



# What is a 2D-Material?

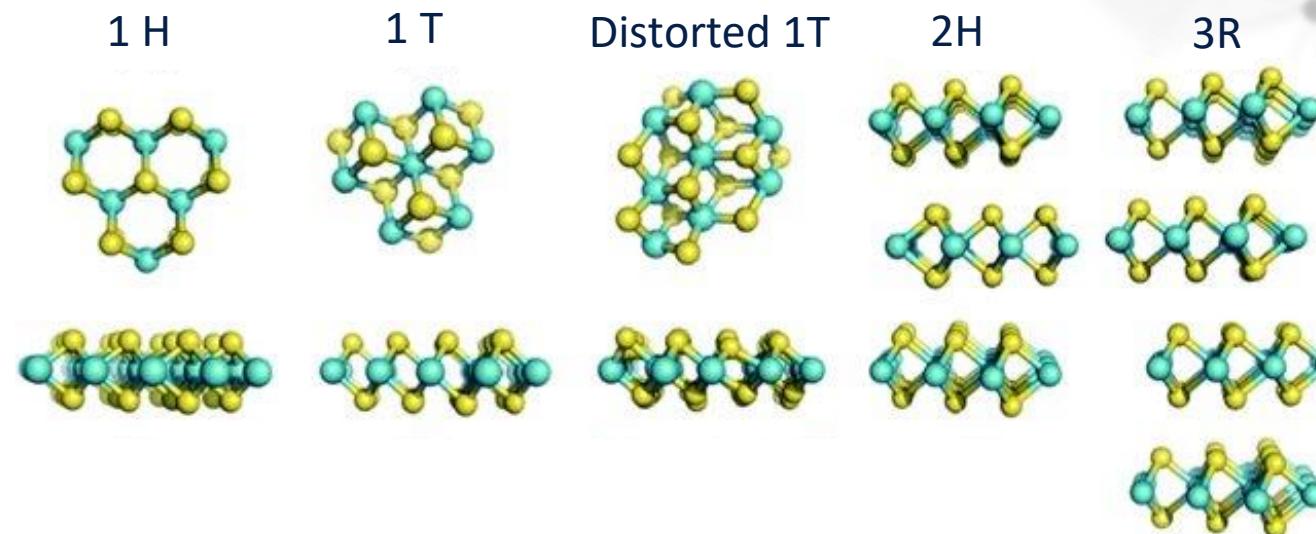


- Strict definition
  - One layer with thickness of one atom
  - Graphene



- ISO/TS 80004-13:2017
  - Layered with strong bonds in each layer
  - Thickness in the nanoscale
  - Properties different from bulk material
  - Transition metal dichalcogenides

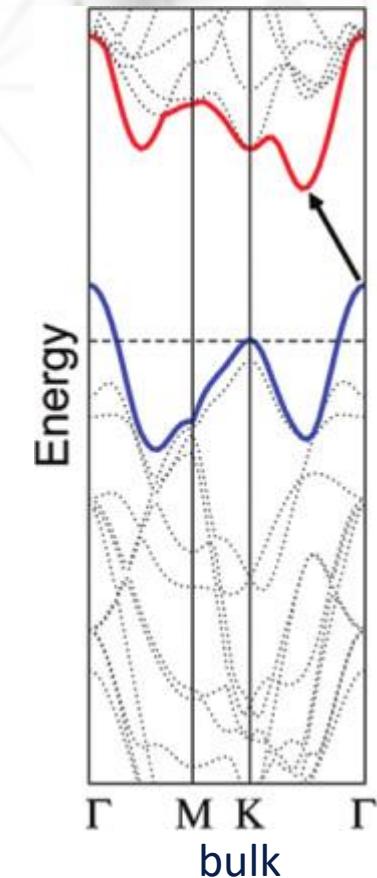
# Molybdenum Disulfide ( $\text{MoS}_2$ )



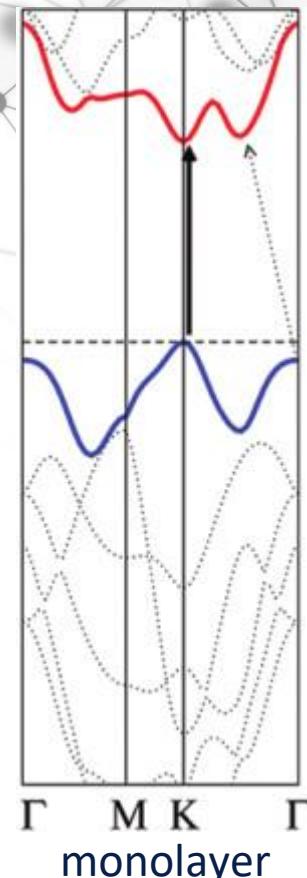
- Semiconducting 1H-phase most common
- 1T-phase metallic
- One S-Mo-S-layer 0.65 nm thick
- Stacking of 1H-phase
  - AB sequence (2H)
  - ABC sequence (3R)



Calculated bandstructure



$\Gamma$  M K  $\Gamma$   
bulk



$\Gamma$  M K  $\Gamma$   
monolayer

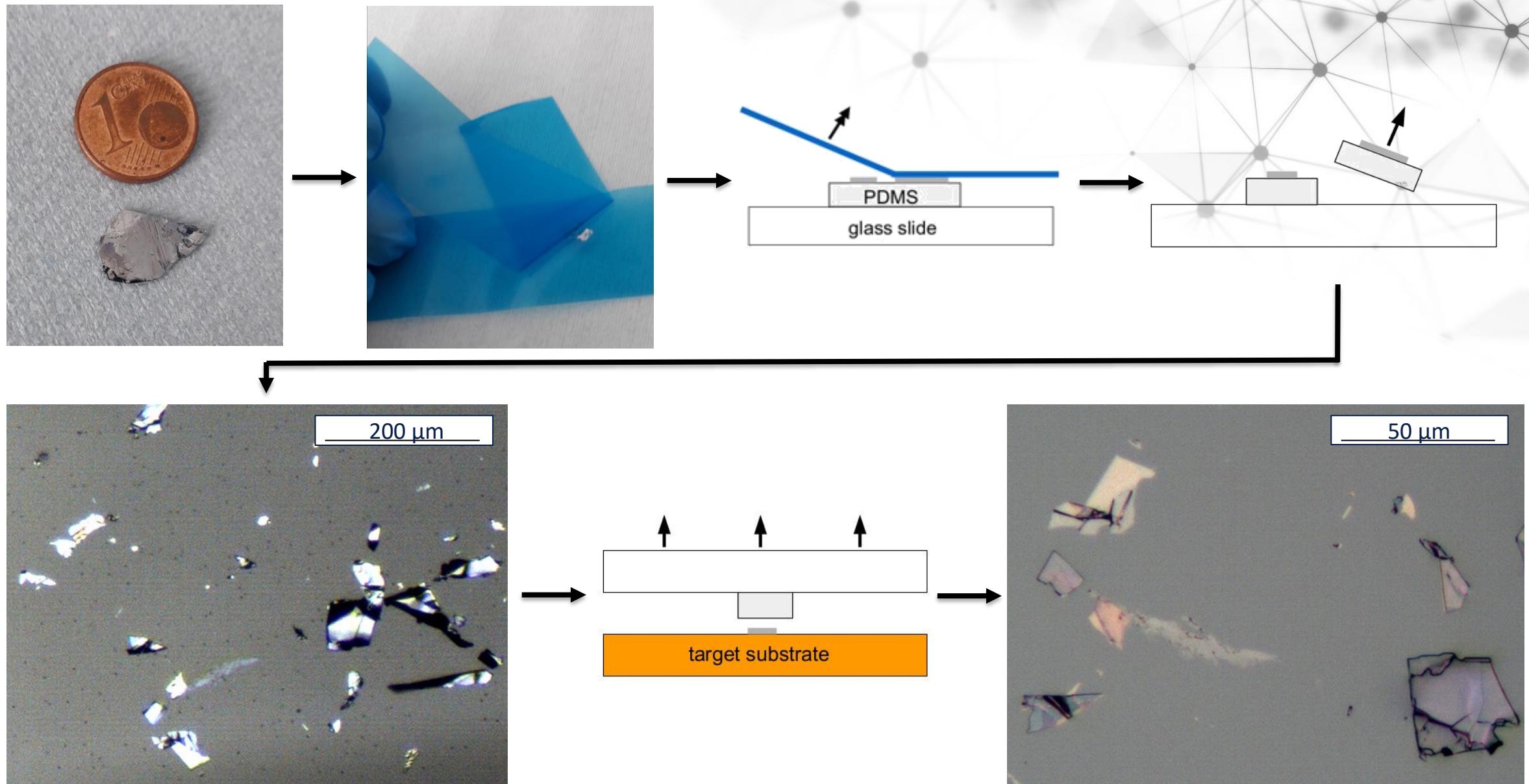
- Bulk: indirect band gap of  $\sim 1$  eV
- Monolayer: direct band gap of  $\sim 1.9$  eV

Voiry *et al*, Chemical Society Reviews 44.9 (2015) 2702

Wang *et al*, Nature nanotechnology 7.11 (2012) 699

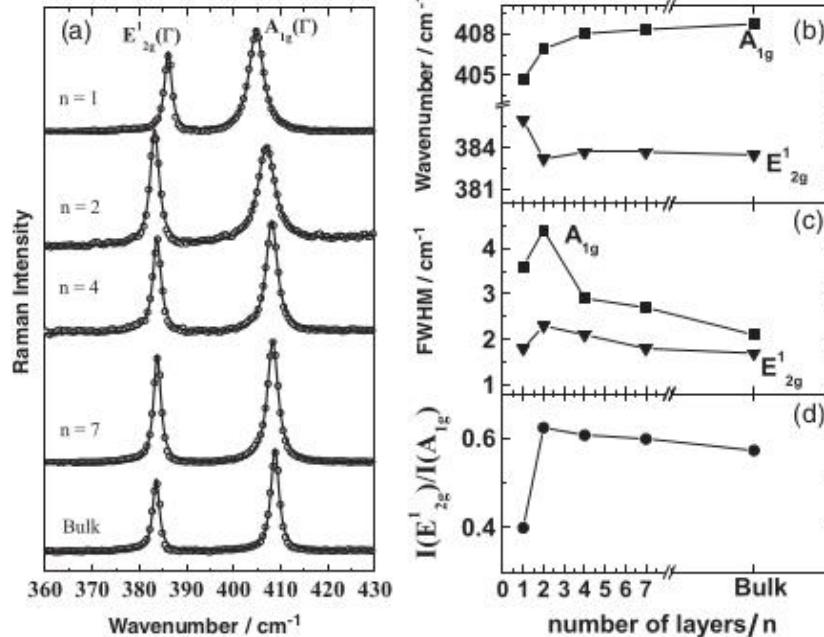
Splendiani *et al*, Nano Lett. 10 (2010) 1271

# Preparation Procedure

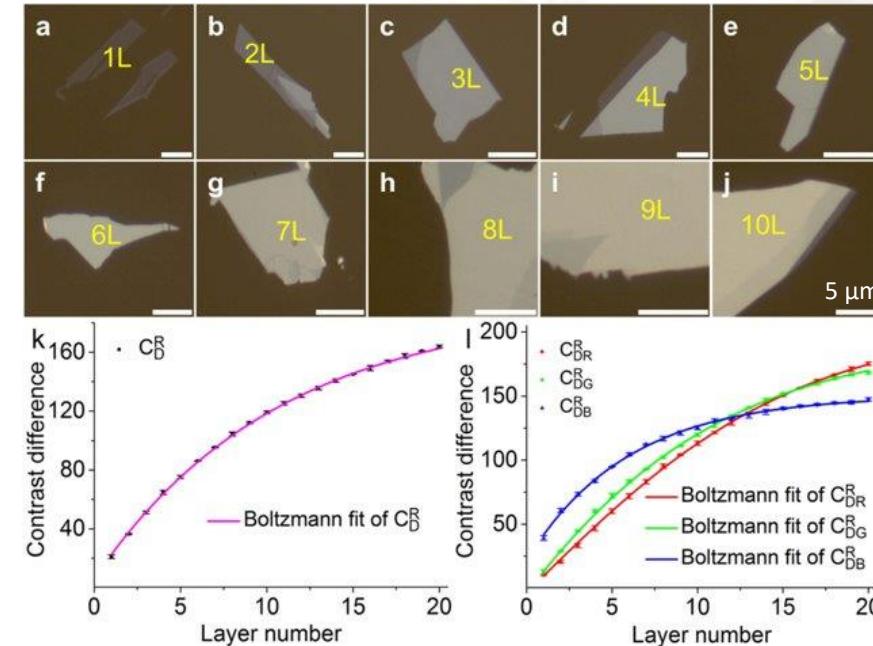


# Thickness Determination

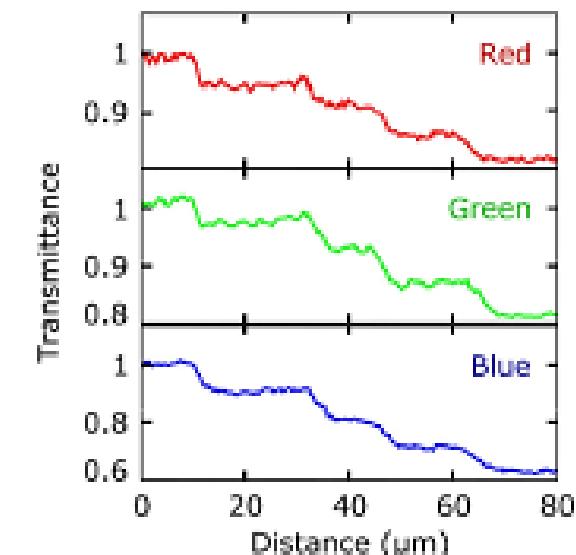
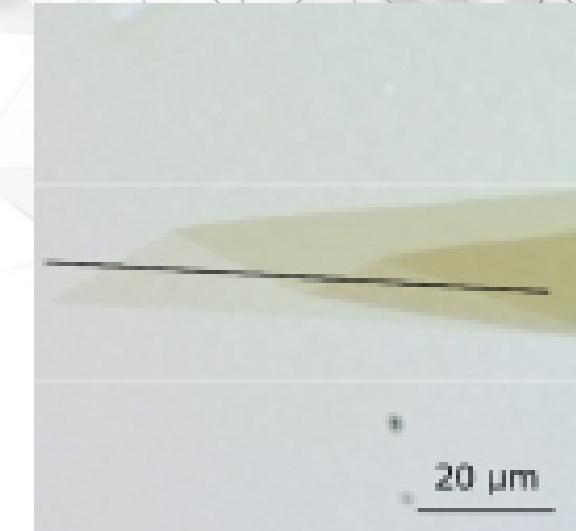
## Raman spectroscopy



## Reflection of light



## Transmission of light



- Determination via optical microscopy before transfer process most practical method

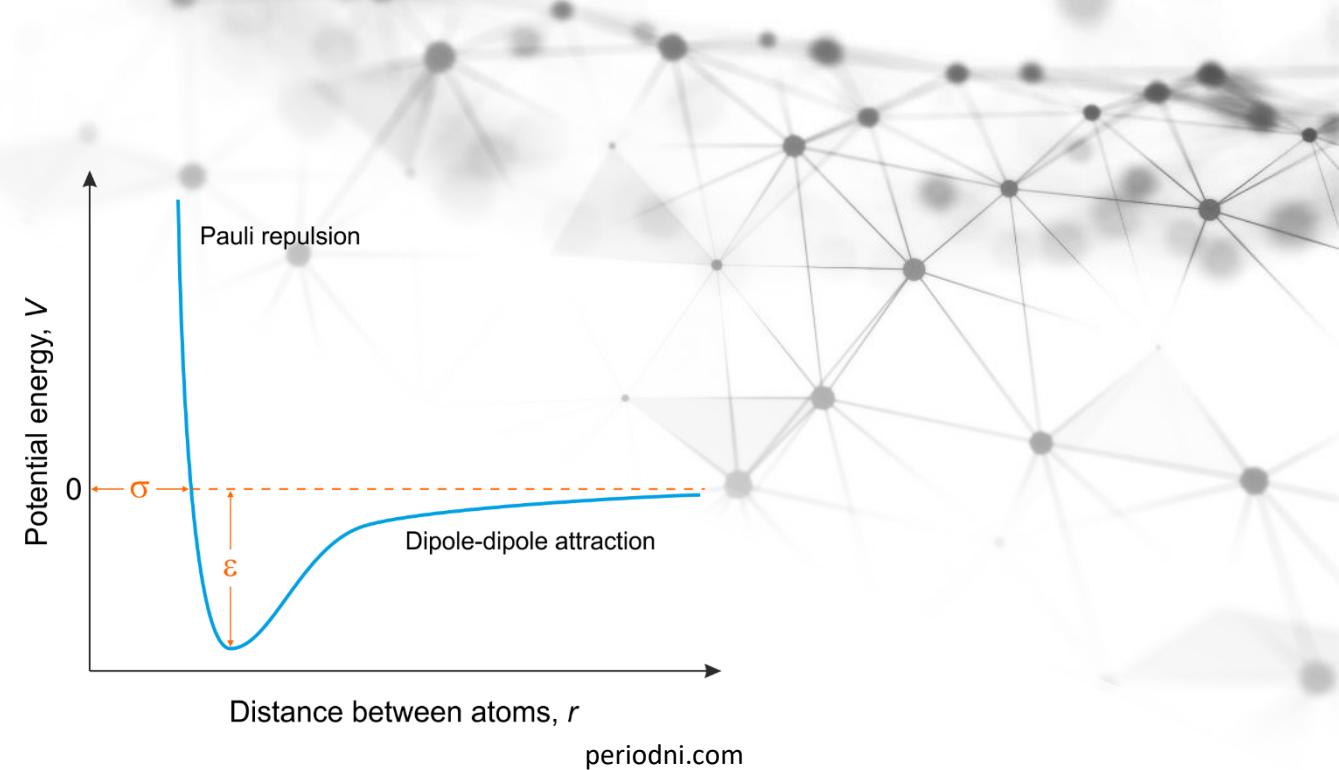
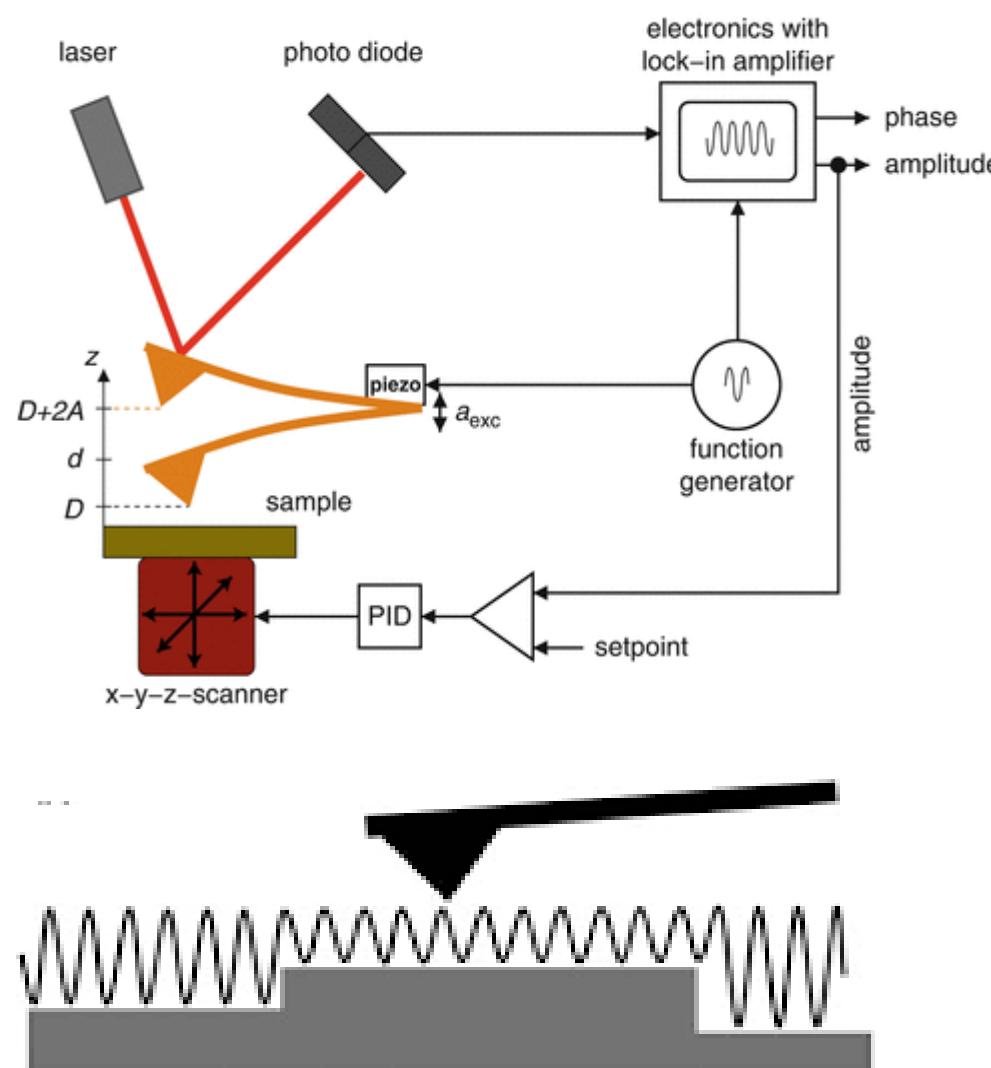
→ Reference measurements with AFM

Chakraborty *et al*, J. Raman Spectroscopy 44 (2013) 92

Zhang *et al*, Nanotechnology 28 (2017) 164001

Taghavi *et al*, Nano Research 12.7 (2019) 1691

# Atomic Force Microscopy

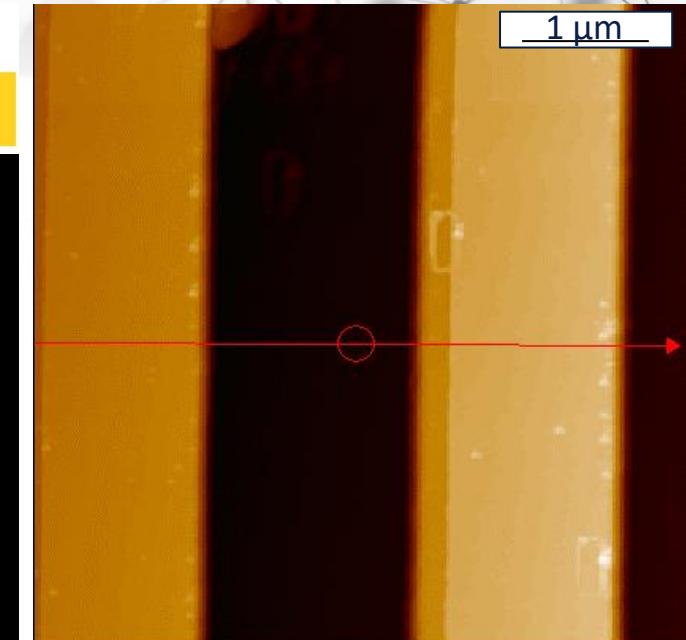
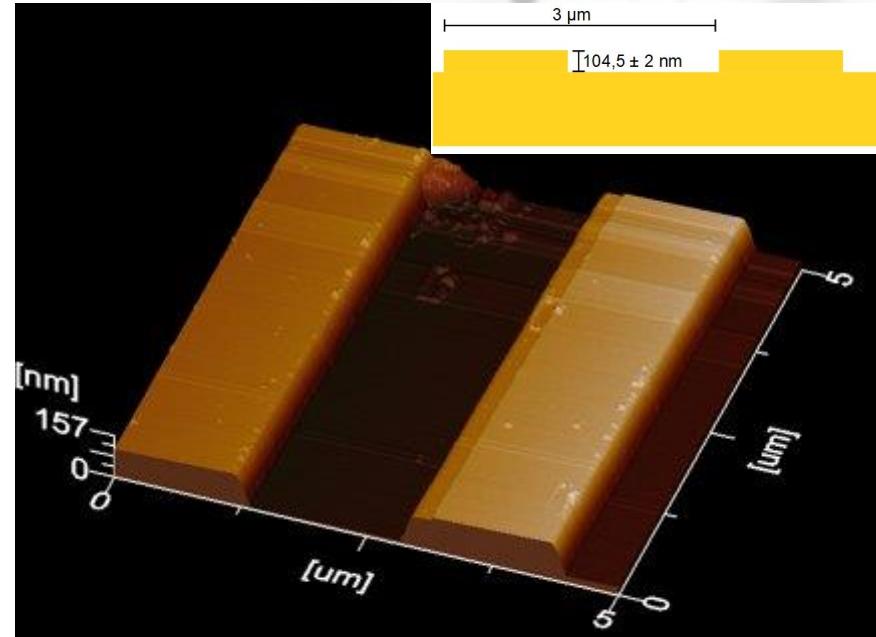
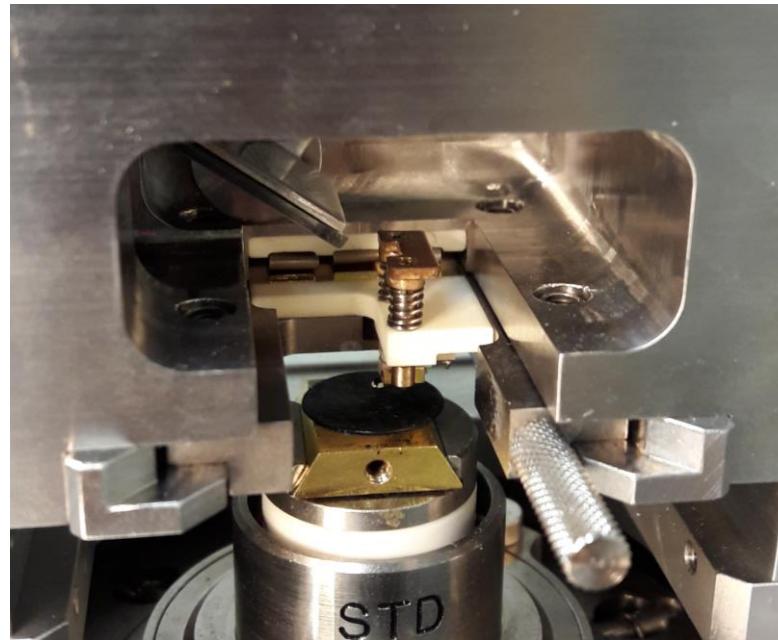


- Cantilever with tip scans the sample
- Tapping mode
  - Oscillating cantilever
  - Change of amplitude due to interaction with sample
  - Feedback loop adjusts height to keep amplitude constant
  - Height adjustments contains topographic information

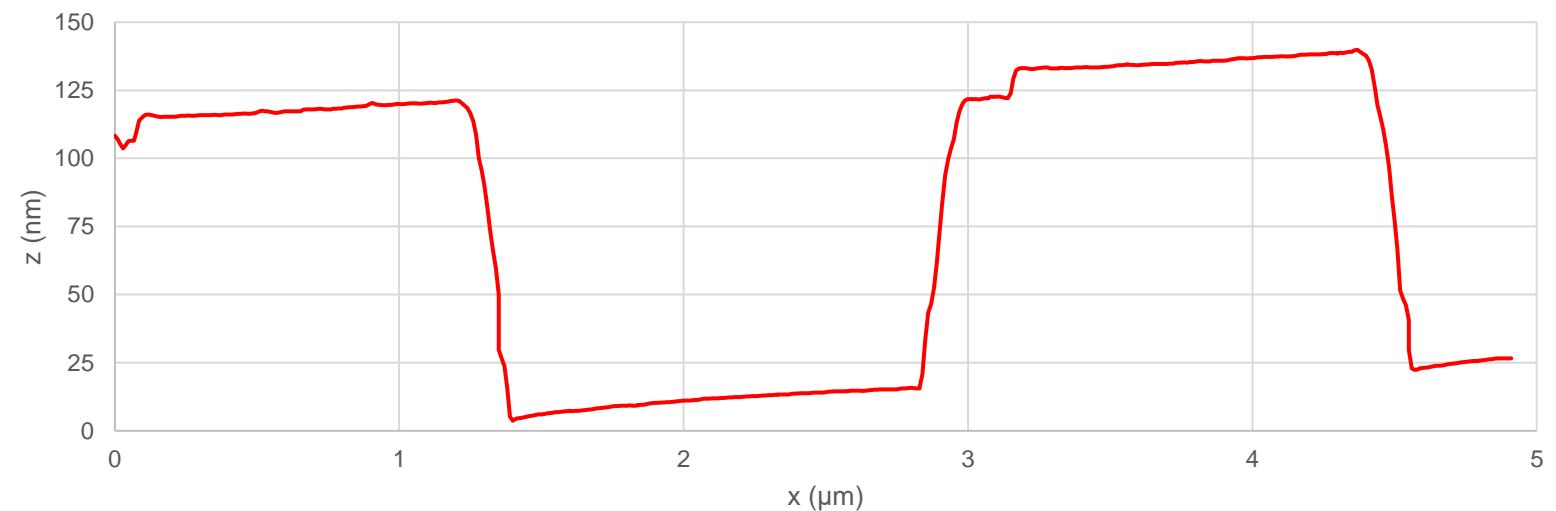
Hölscher, Encyclopedia of Nanotechnology (2012)

Averett and Schoenfisch, Analyst 135 (2010) 1201

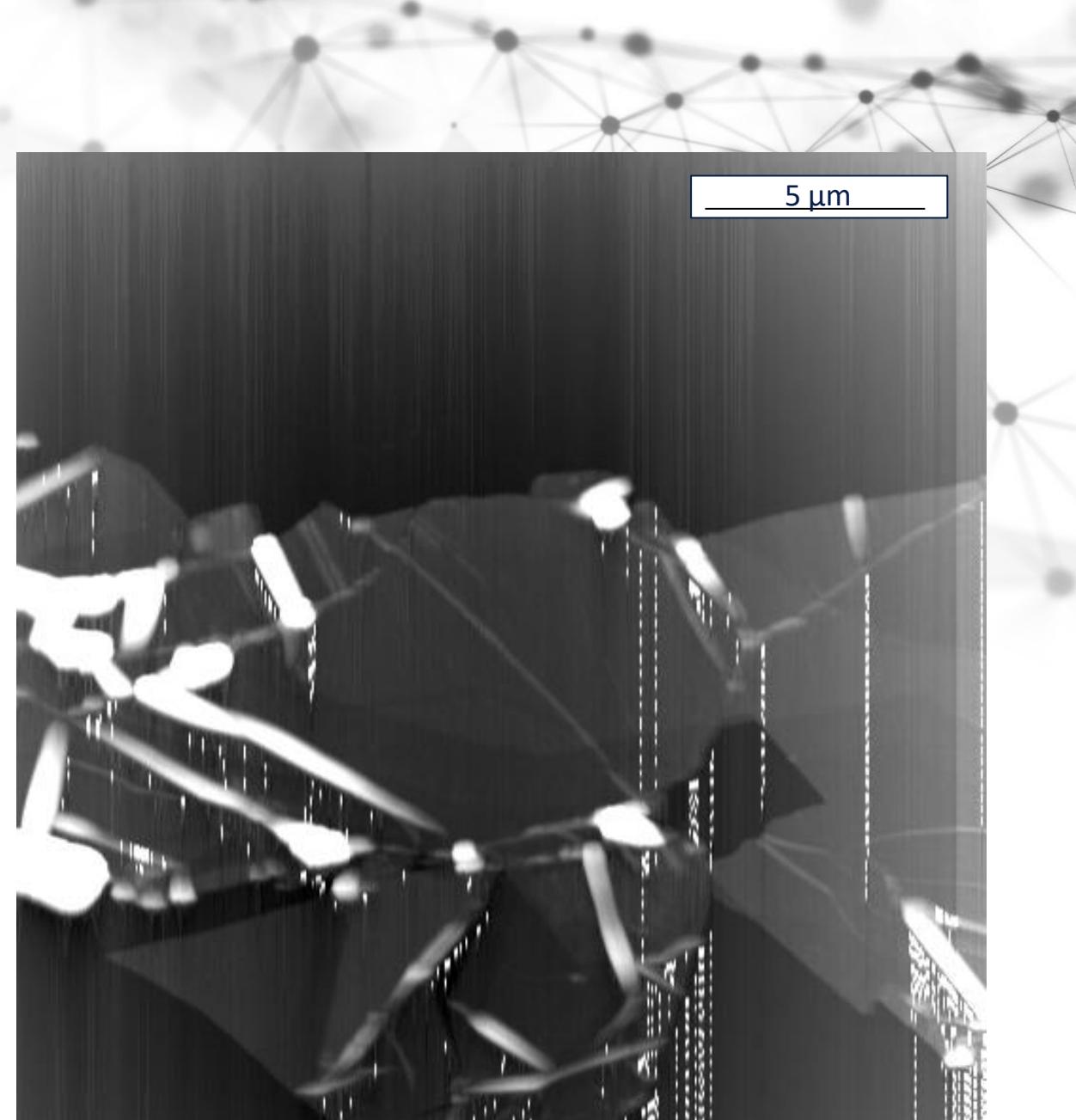
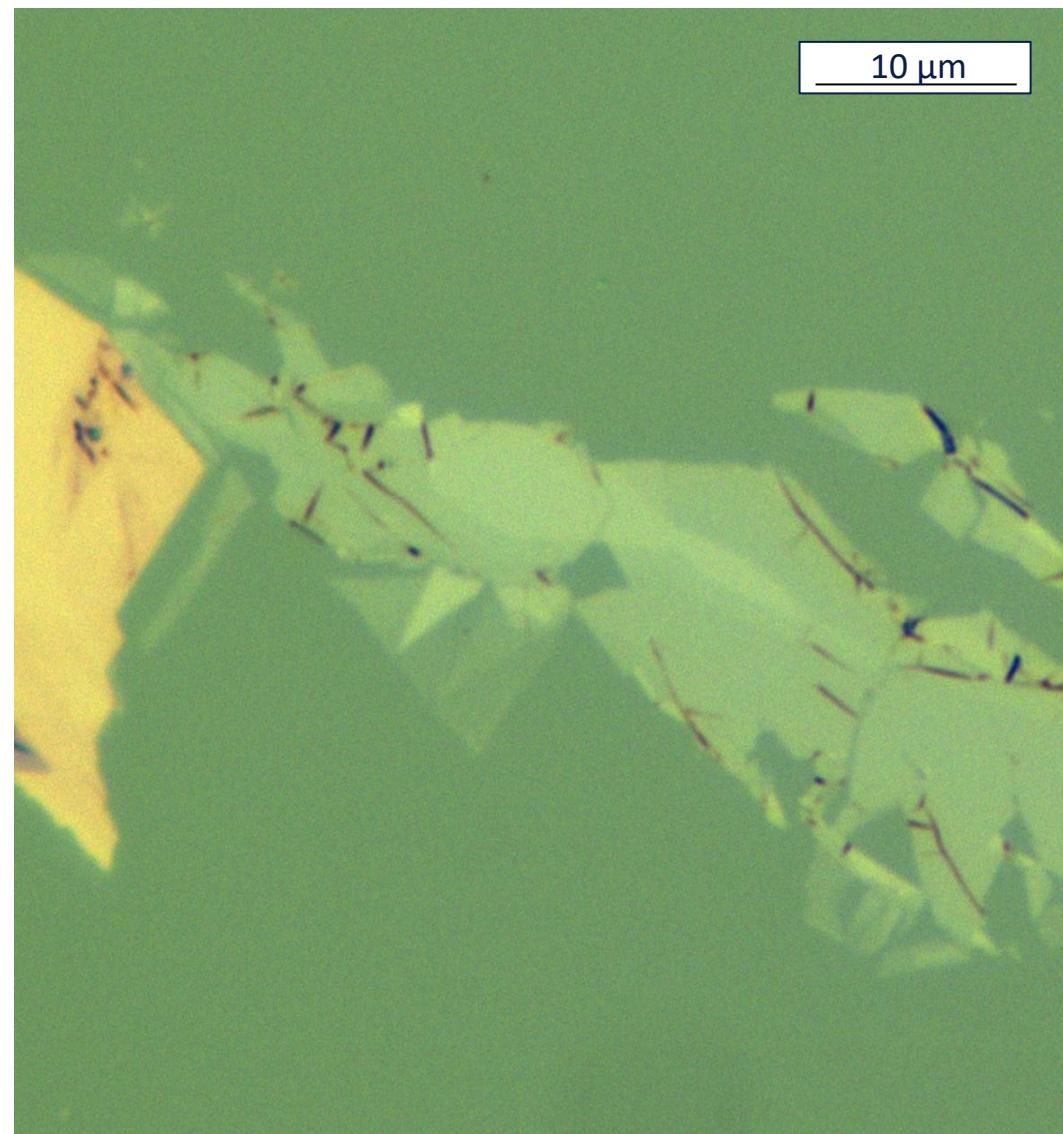
# AFM Reference Sample



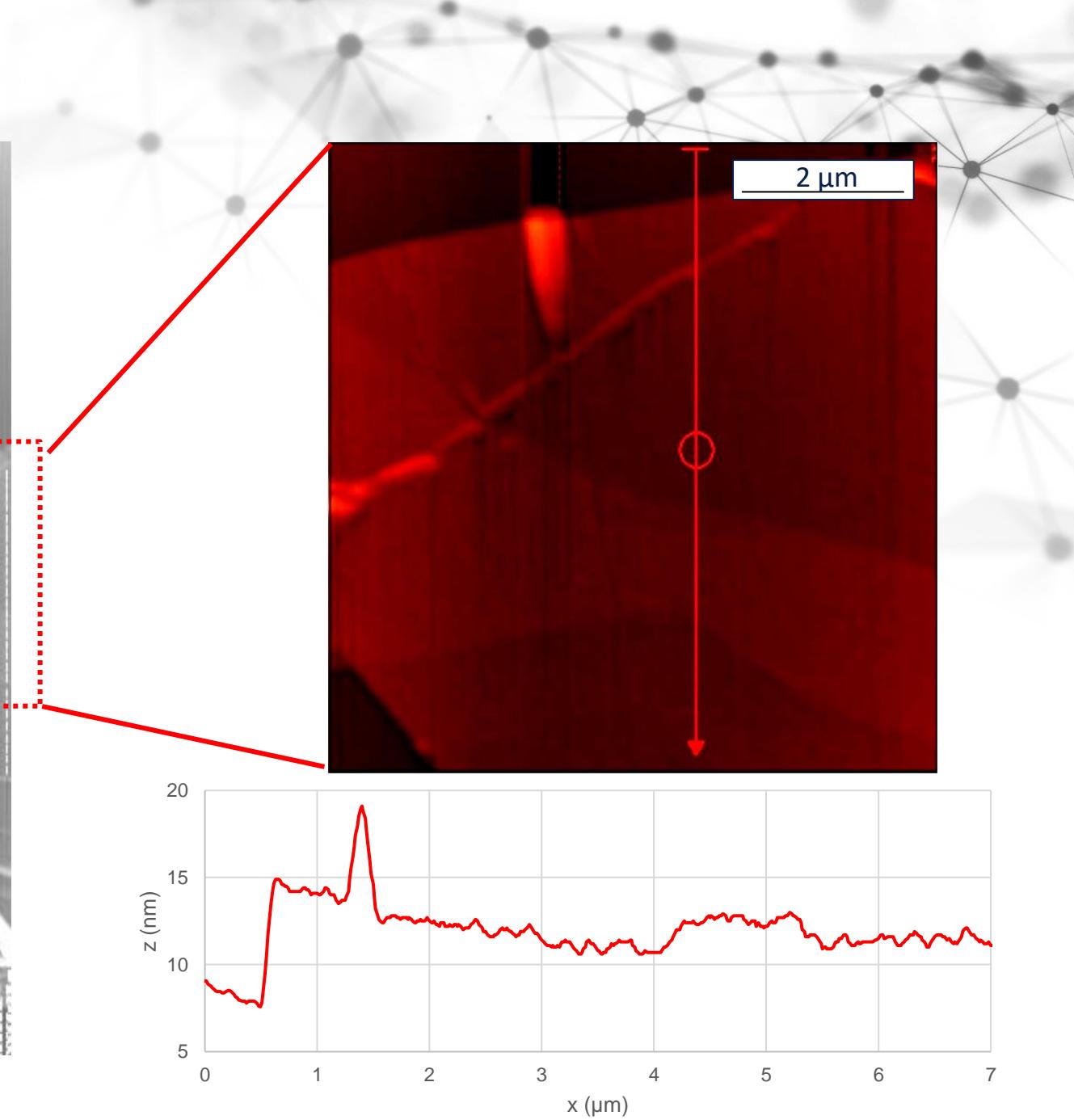
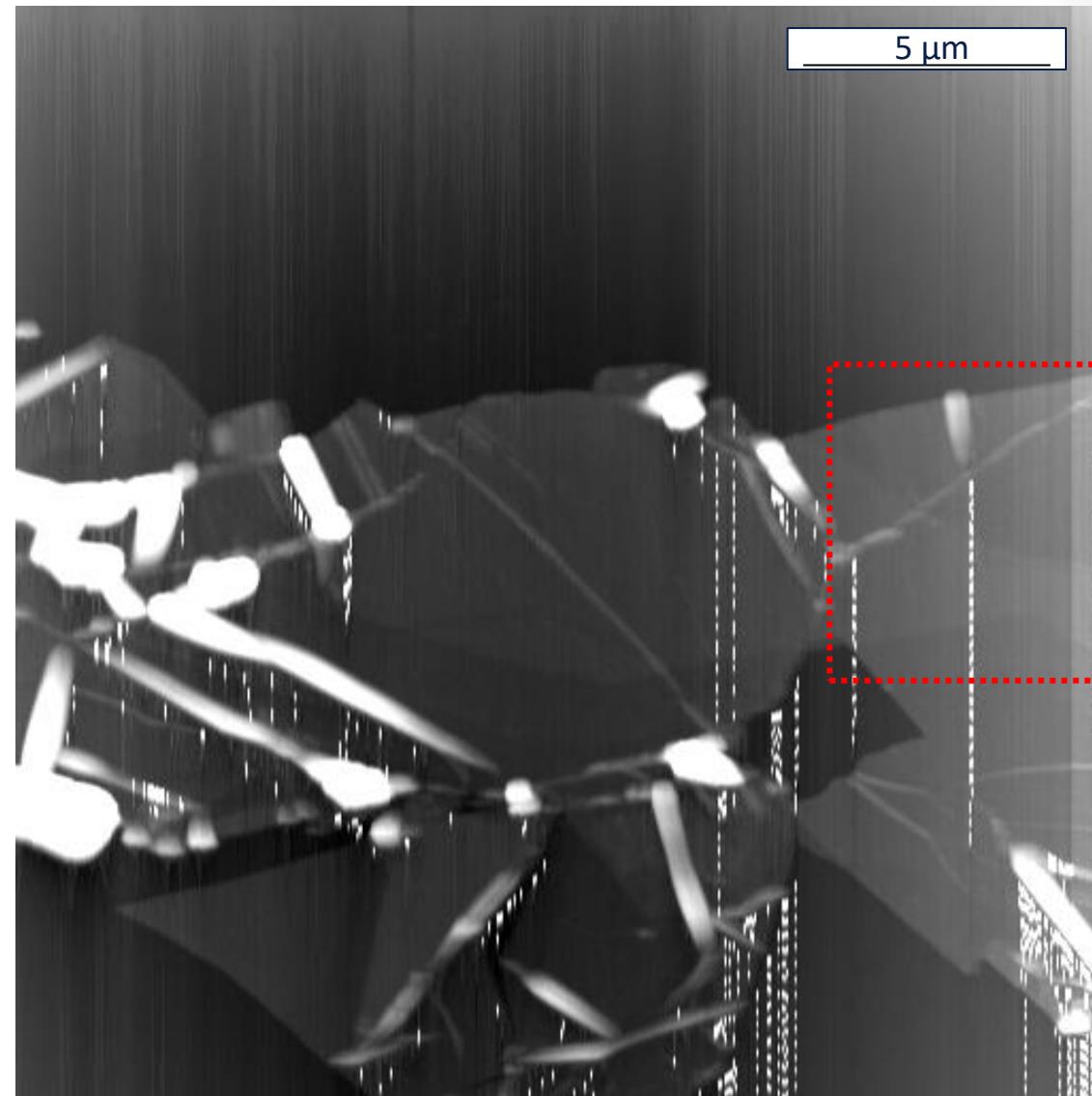
→ Deviation in z - measurement



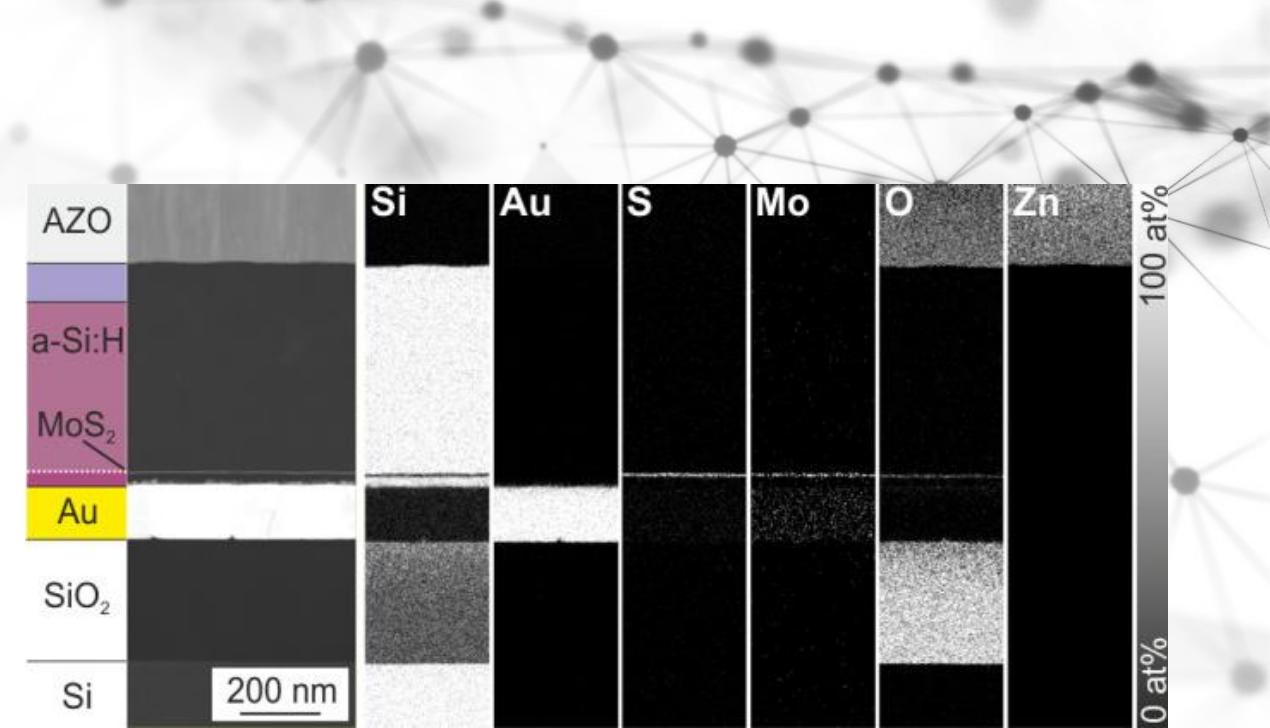
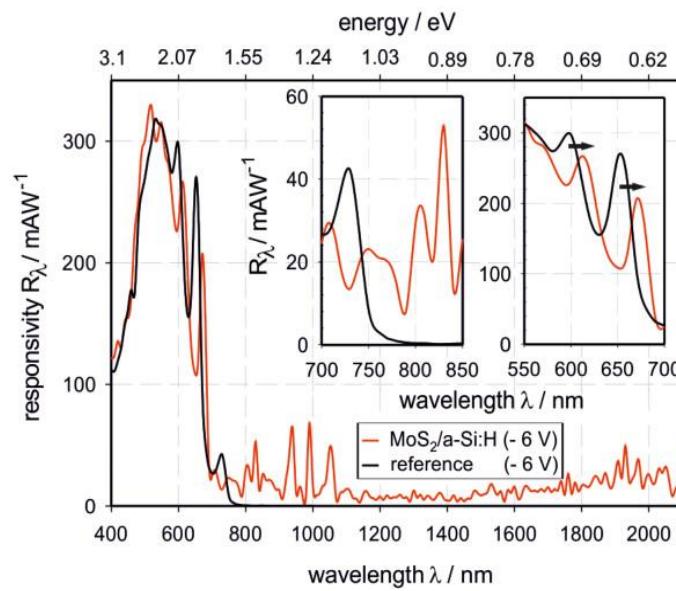
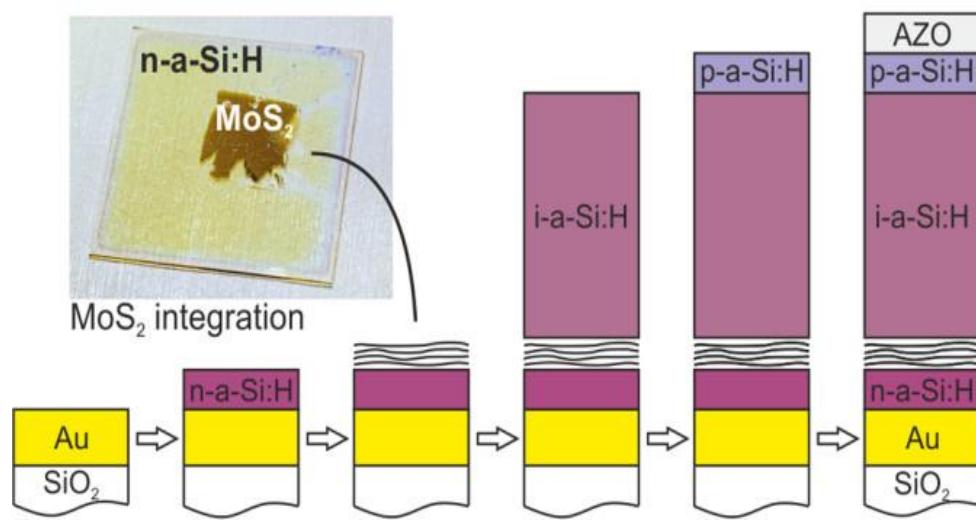
# First AFM Measurements



# First AFM Measurements



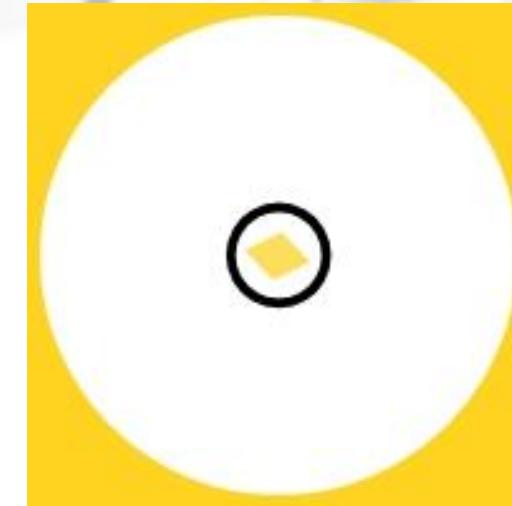
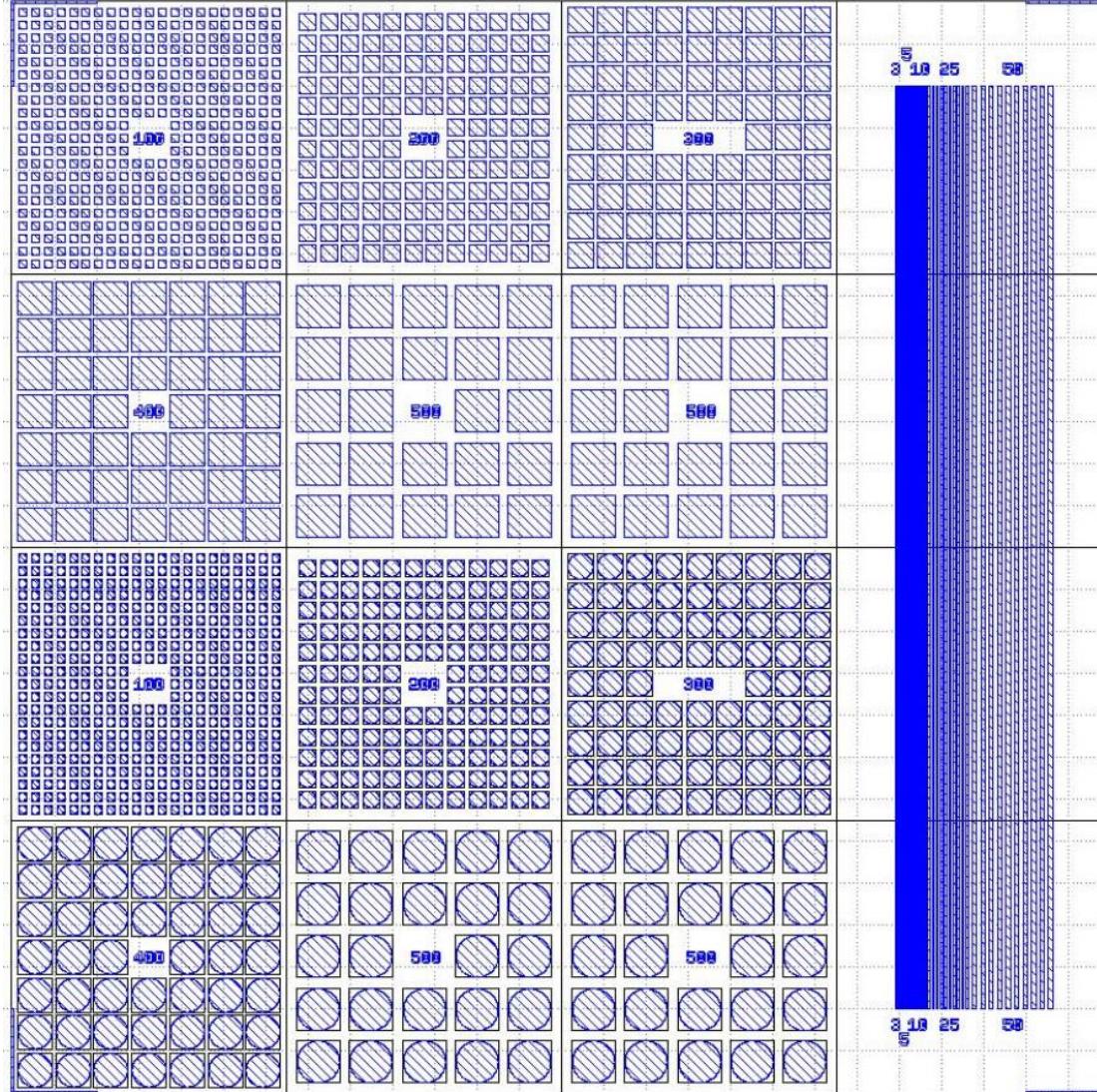
# Device Integration - MoS<sub>2</sub>/a-Si:H Photodiode



- Responsivity in infrared range by adding a layer of MoS<sub>2</sub>
- 4 nm thick thermally assisted converted MoS<sub>2</sub>
- Unknown structure of the MoS<sub>2</sub> layer  
→

Replacing deposited MoS<sub>2</sub> by exfoliated MoS<sub>2</sub> flakes

# Transfer of MoS<sub>2</sub>-Flakes

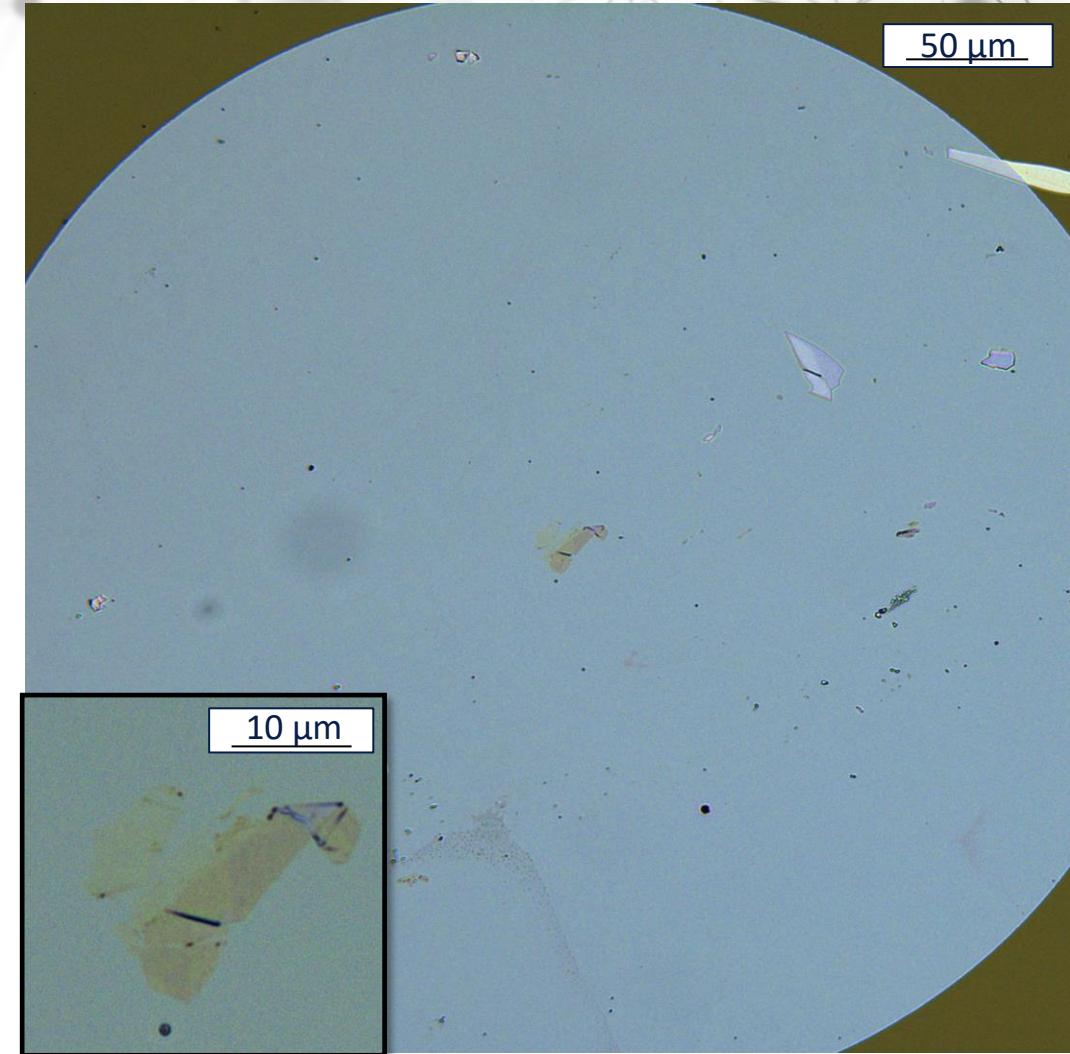
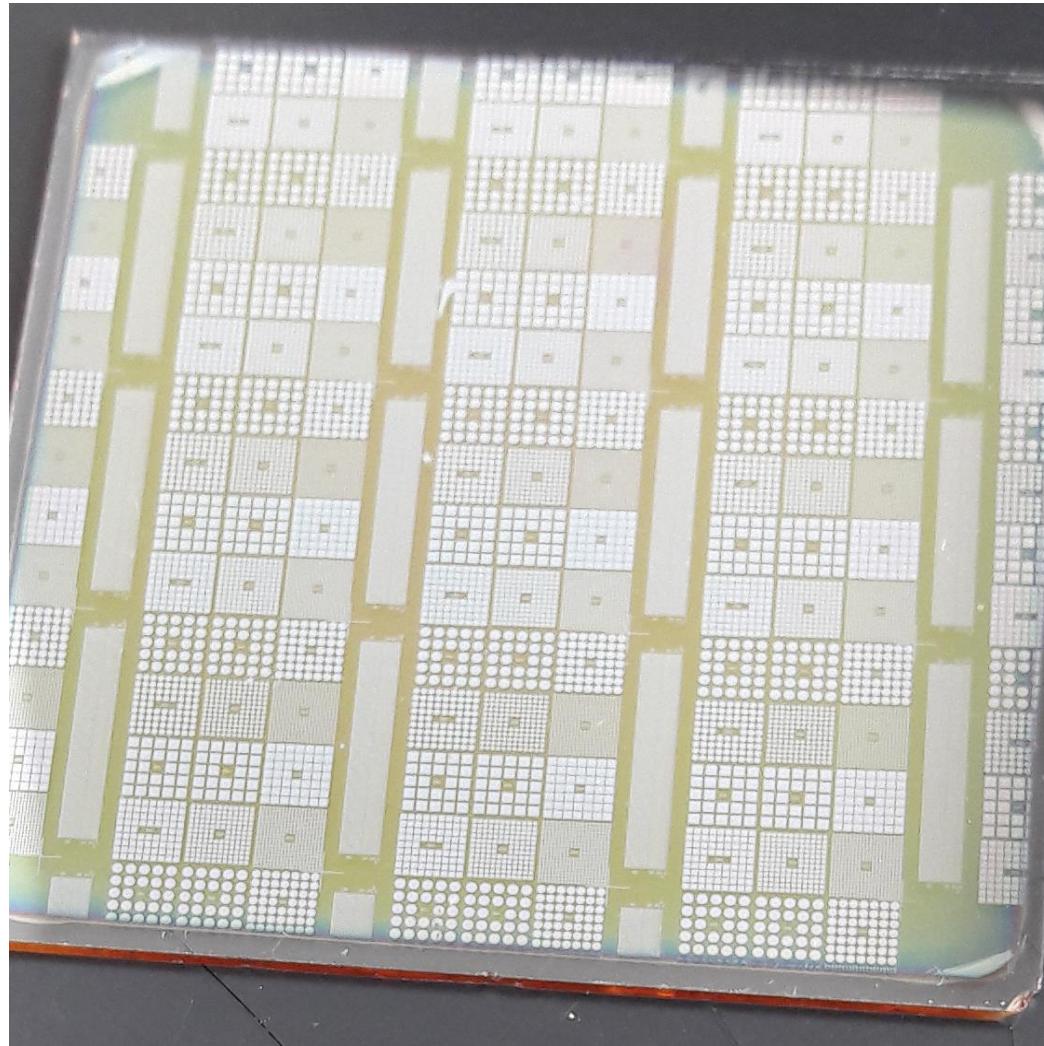


	A	B	C	D	E	F	G	H	I	J
1										
2										
3										
4			X							
5										
6	X									
7					X					
8	X	X								
9										
10										

wikipedia.de

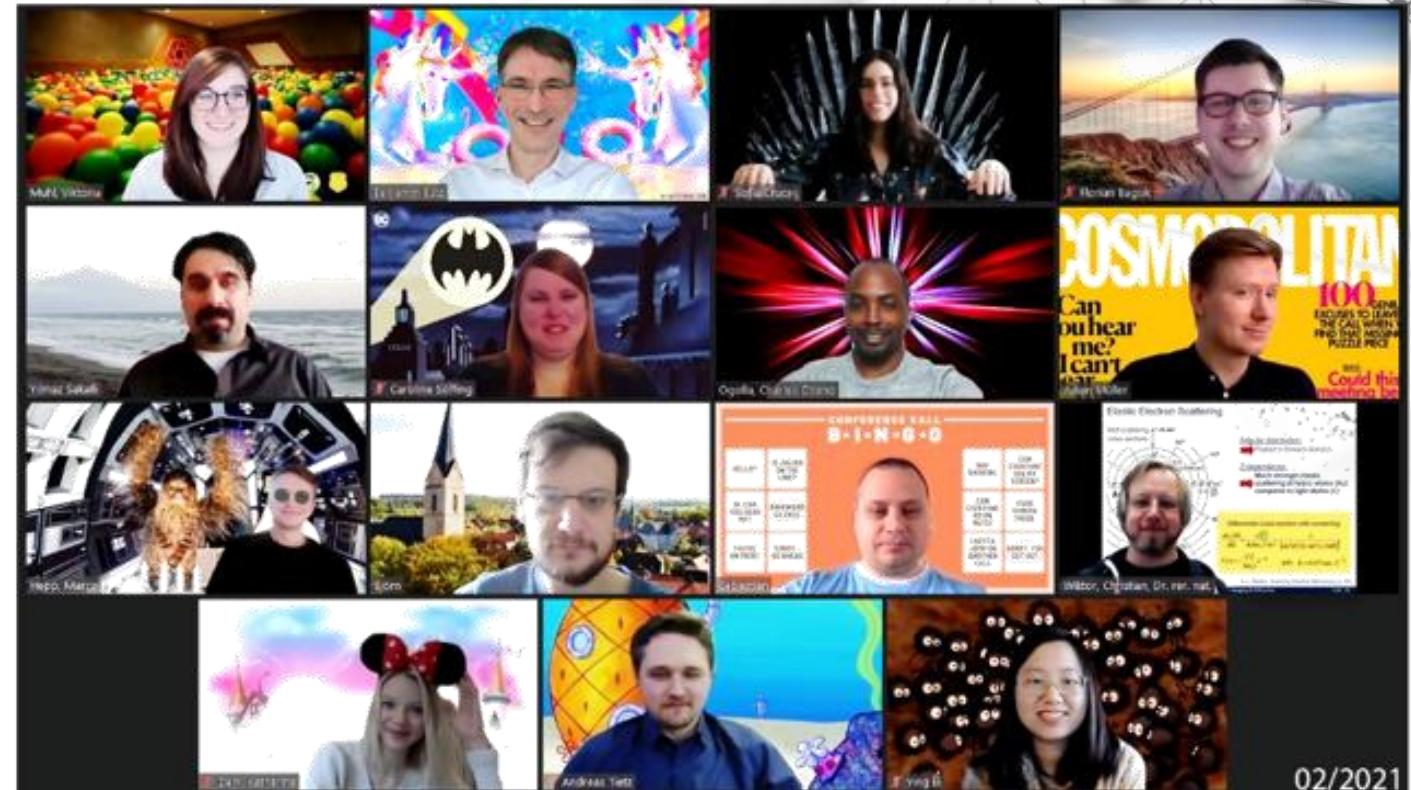
- Flakes with thickness of few layers
- Notation of target location
  - Shape and size of structure
  - In each block by number and letter (like "Schiffe versenken")
- Further processing requires transfer in the middle of one structure

# First Test Transfers



# Acknowledgment

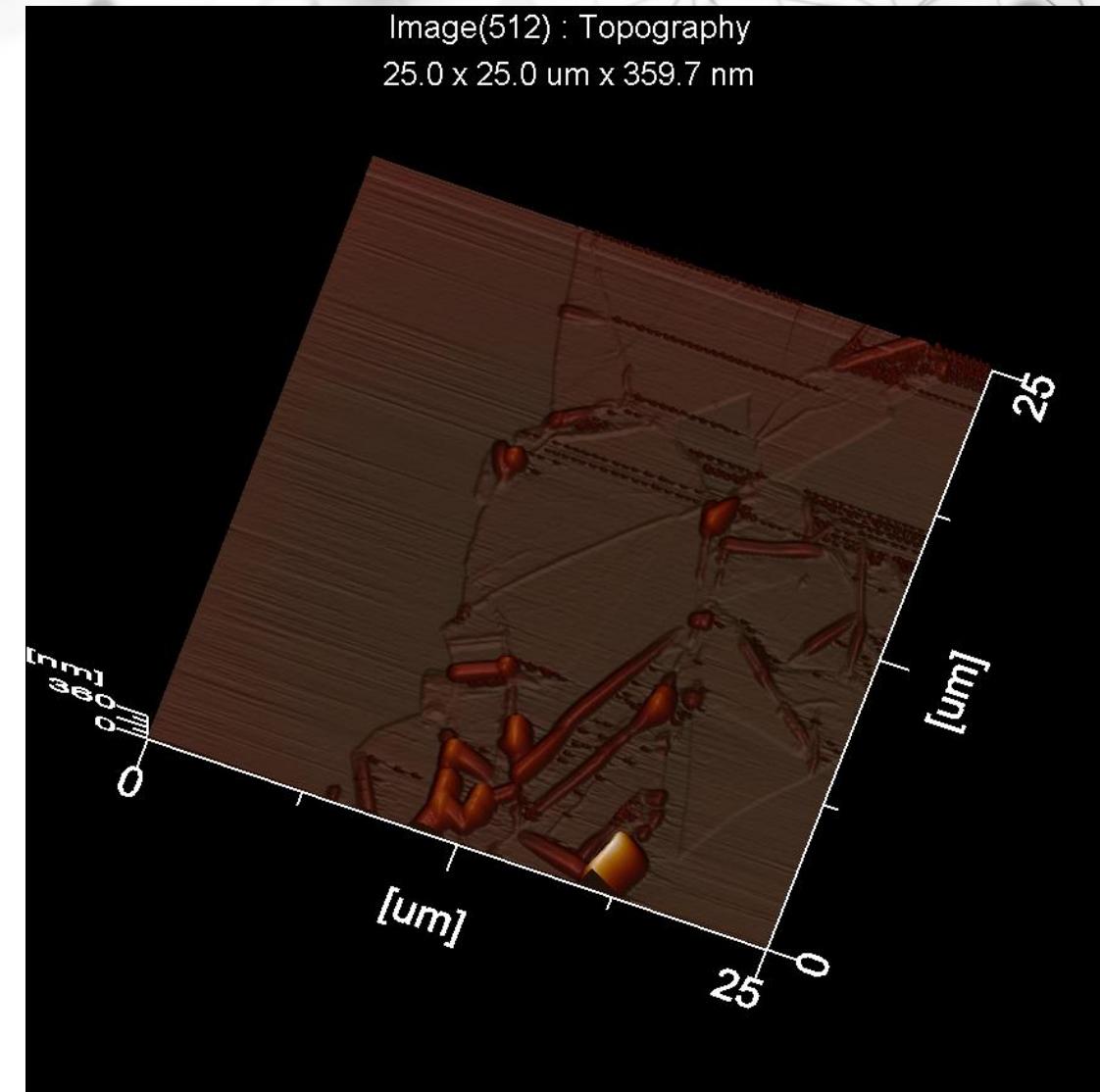
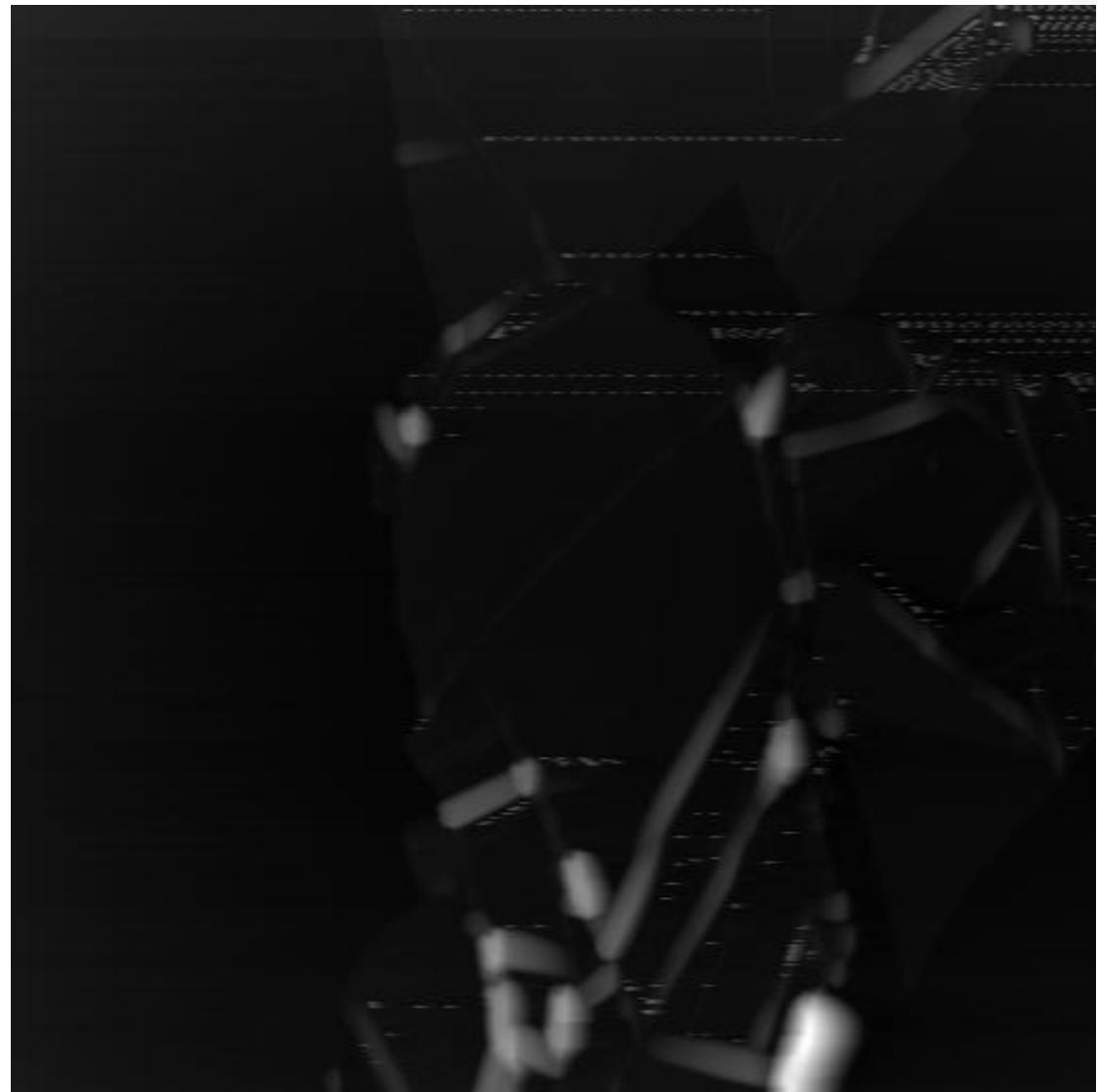
Prof. Benjamin Butz  
Charles Otieno Ogolla  
Sofia Cruces  
Dr.-Ing. Julian Müller  
Dr. Andreas Bablich  
Patrick Hartwich  
... and many more!

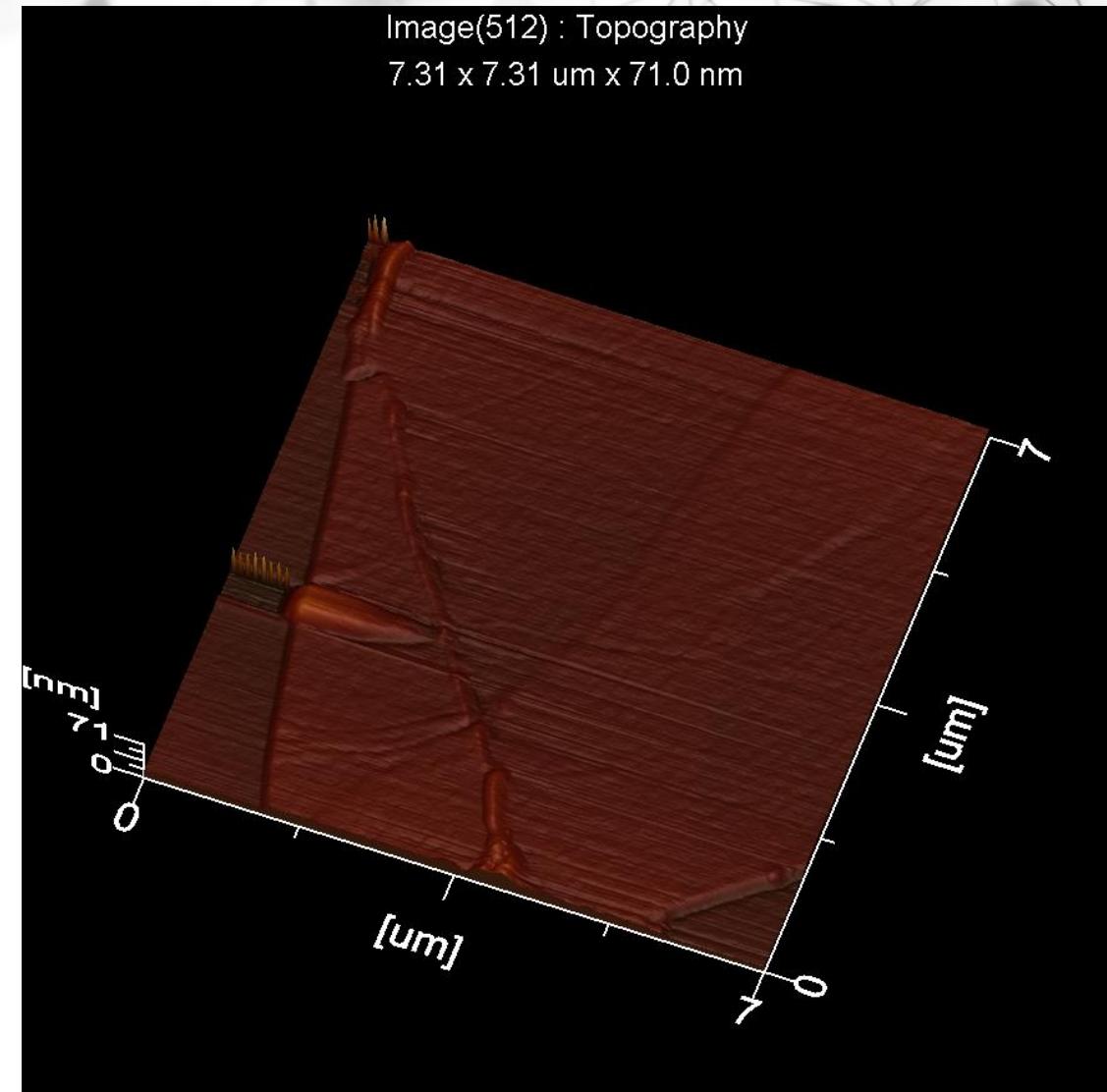
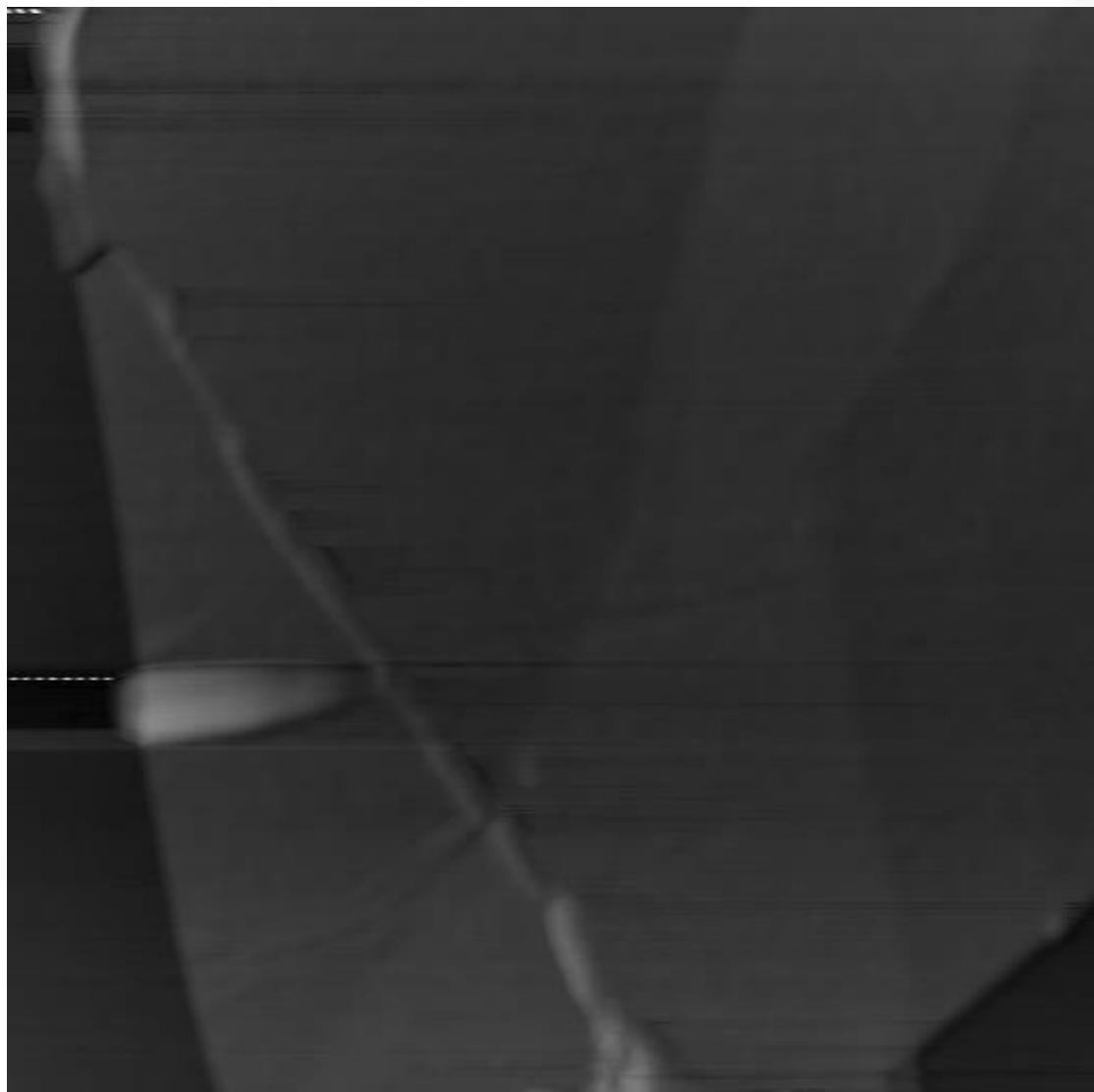


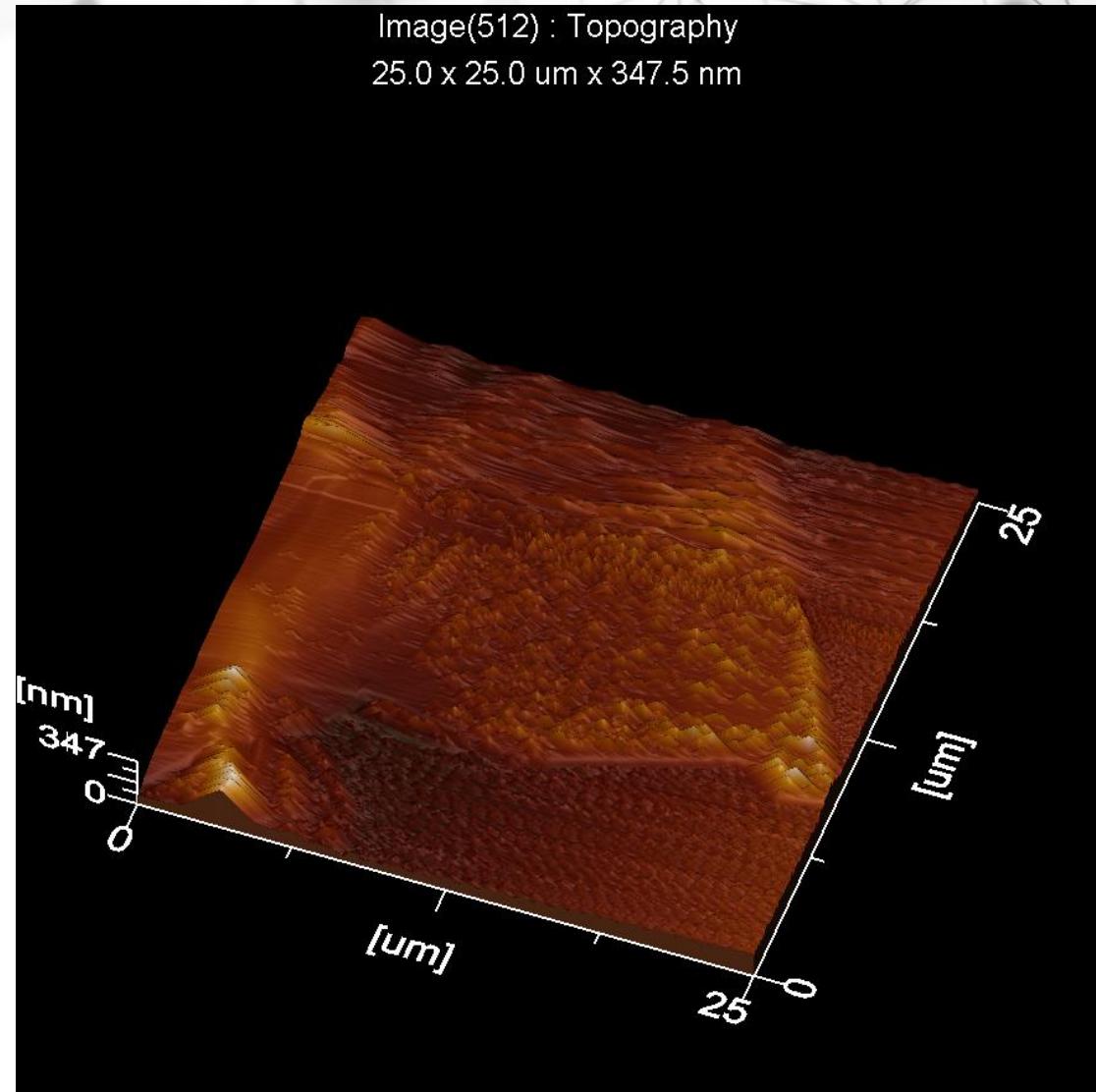
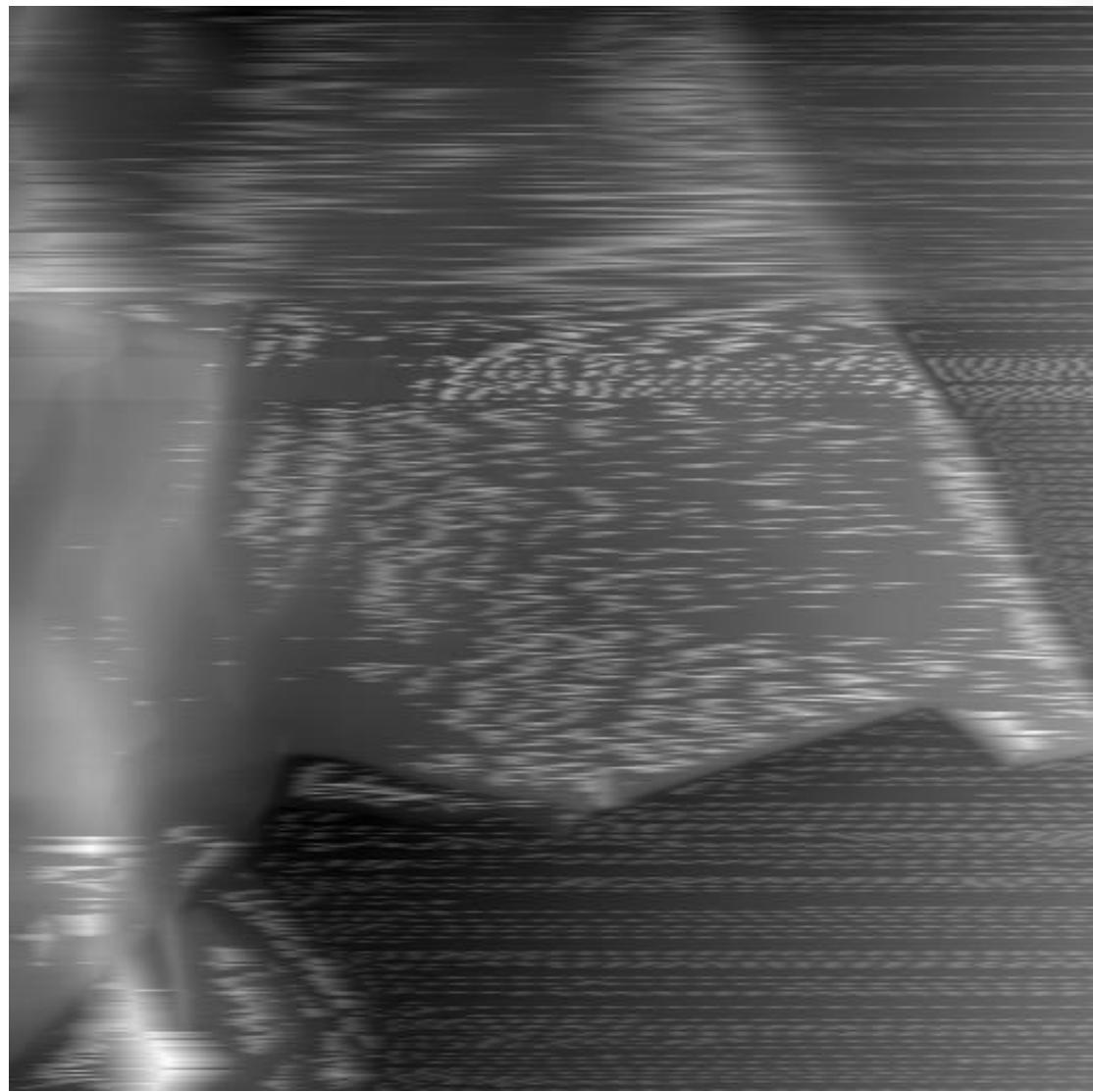


THANK YOU FOR YOUR ATTENTION !

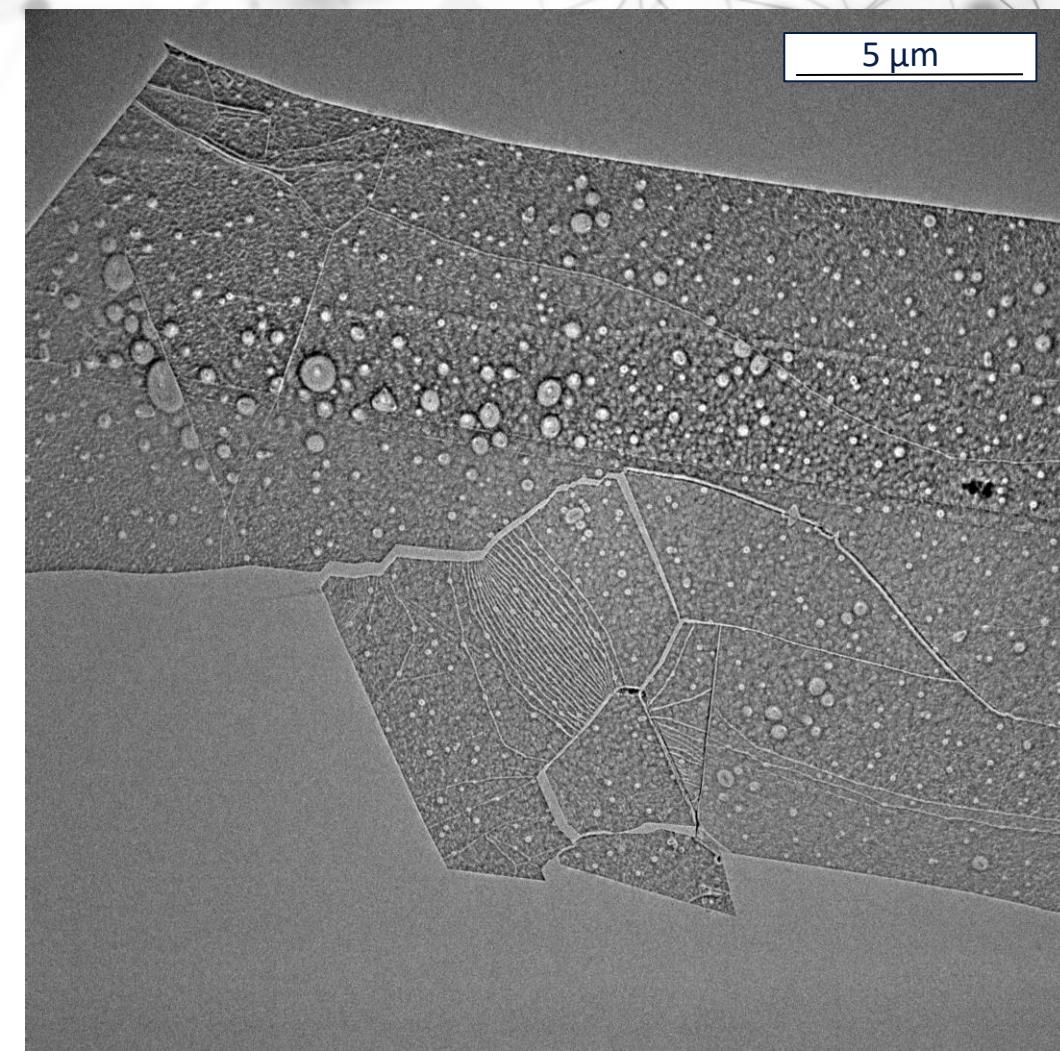
# Extra slides



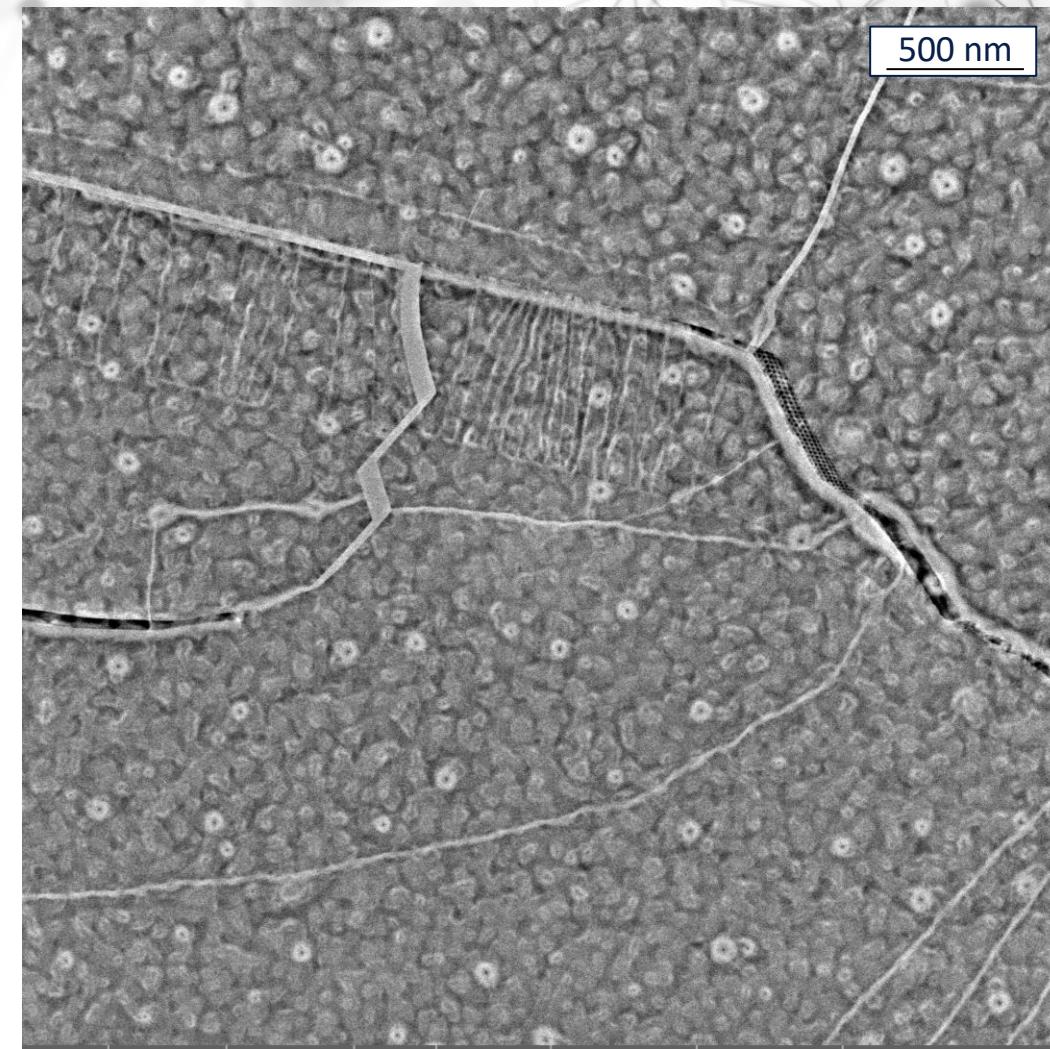
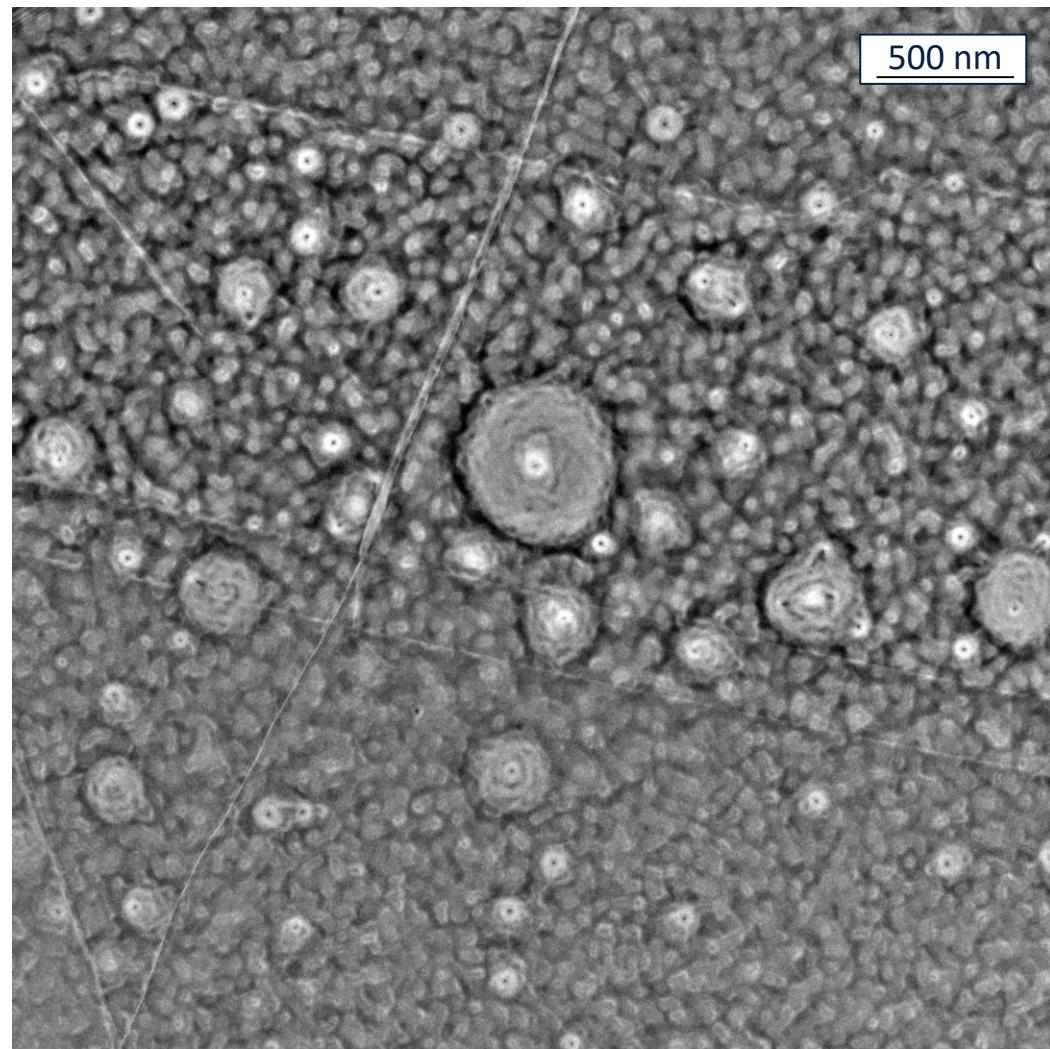




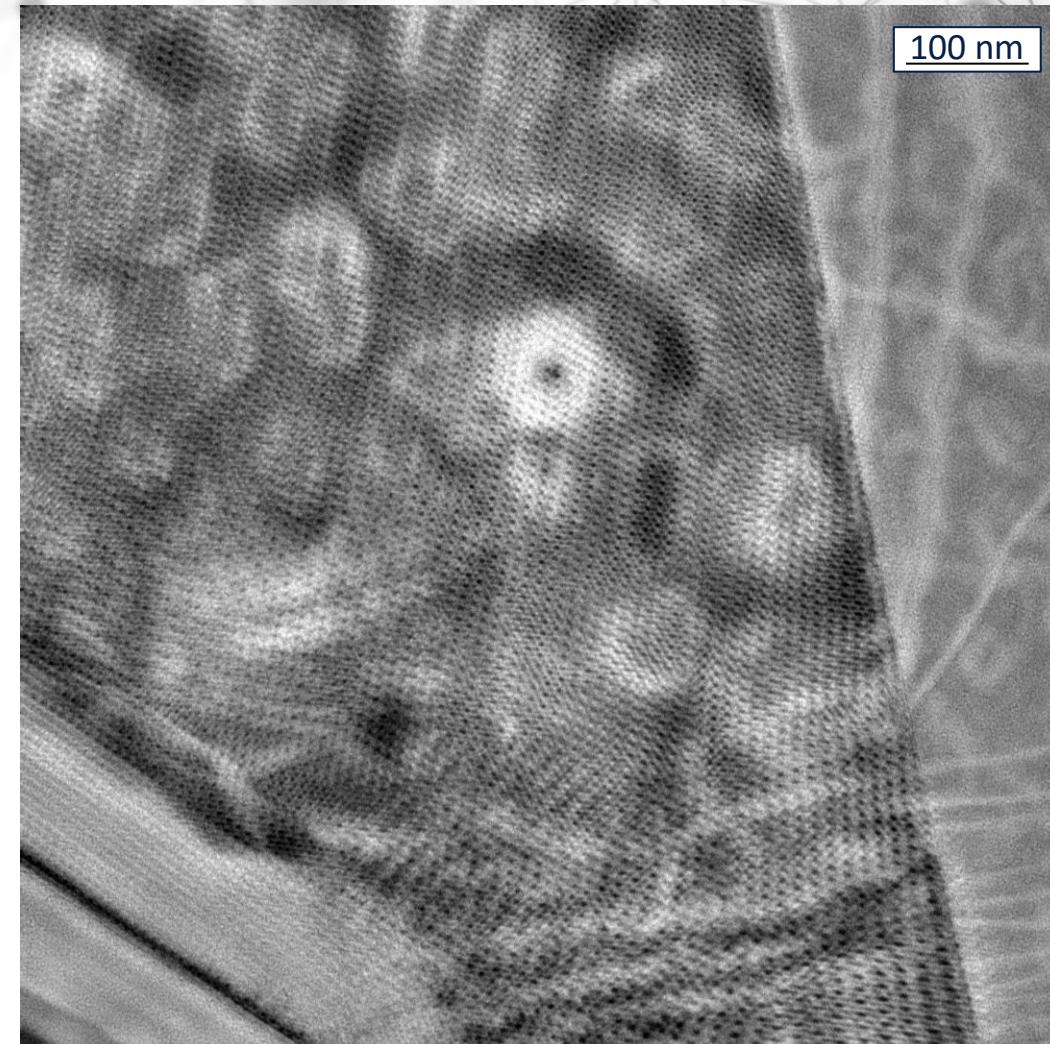
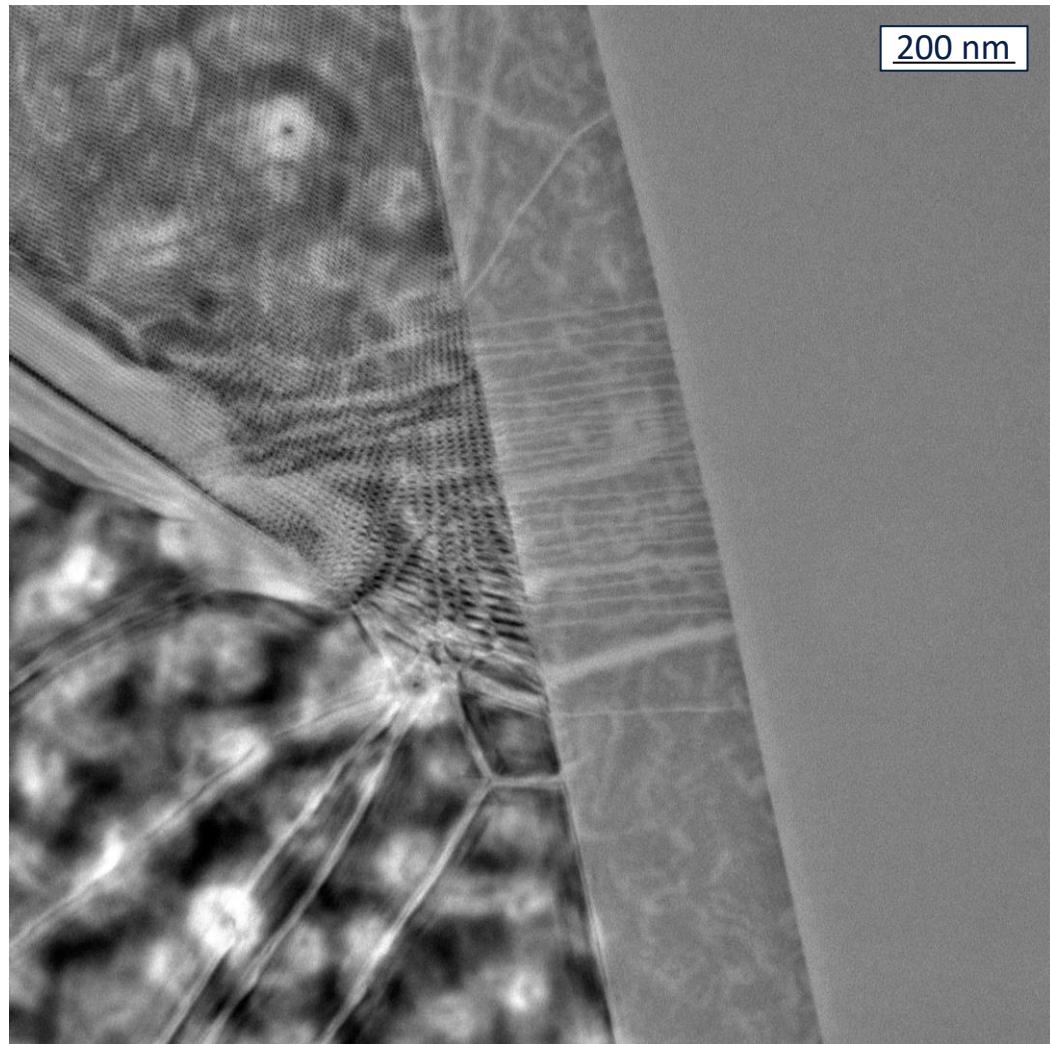
# Defect Characterisation



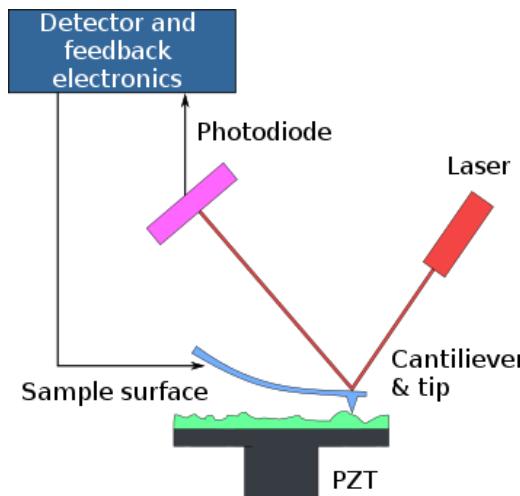
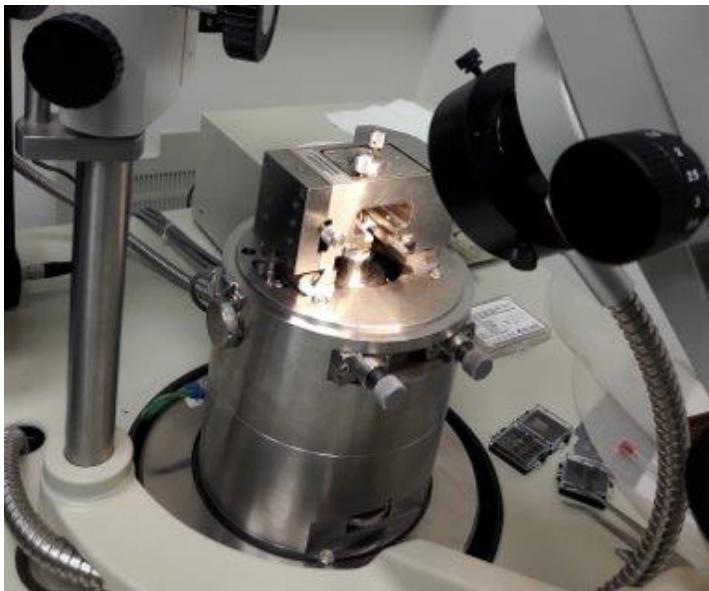
# Defect Characterisation



# Defect Characterisation



# Rumpelkammer



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